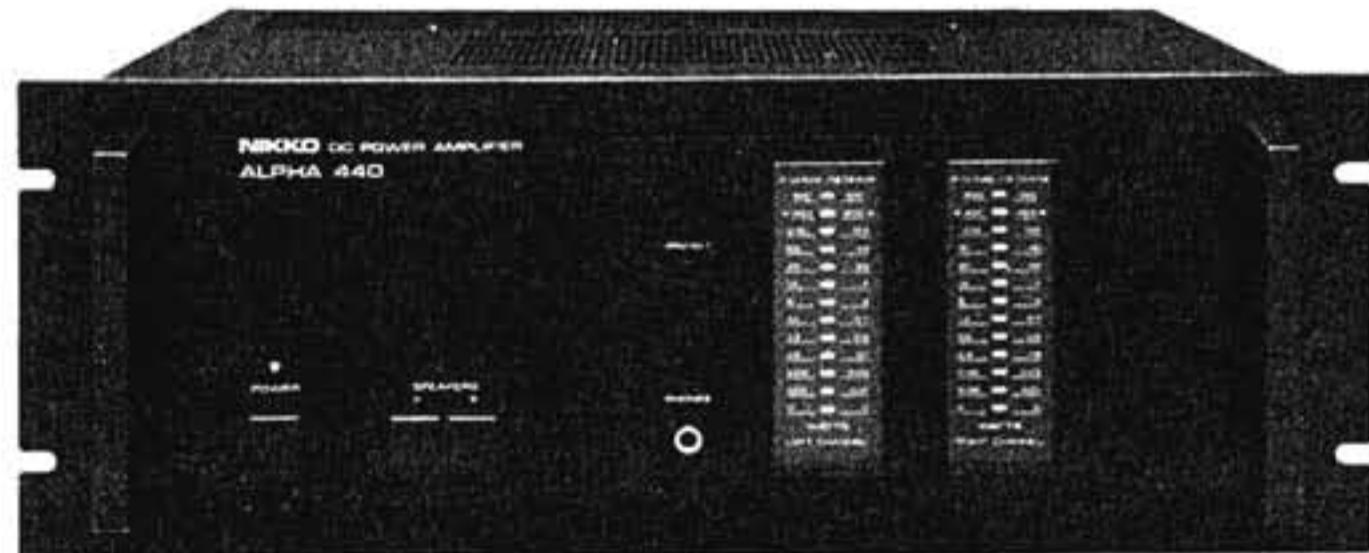


NIKKO**POWER AMP**

ALPHA 440

STEREO POWER AMPLIFIER



TYPE AND VOLTAGE

W-TYPE:	UL and CSA type	120V AC
E -TYPE:	NK-STD type	220V AC
B -TYPE:	BS type	240V AC

SERVICE MANUAL

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SPECIFICATIONS

AMPLIFIER SECTION

Continuous Power Output per Channel:

20 ~ 20000 Hz (8 ohms) more than 220 Watts
20 ~ 20000 Hz (4 ohms) more than 240 Watts
1000 Hz (8 ohms) more than 240 Watts
1000 Hz (4 ohms) more than 240 Watts

T. H. Distortion, 8 ohms:

at Continuous Power Output . . no more than 0.008%
at 1 Watt Power Output no more than 0.02%

T. H. Distortion, 4 ohms:

at Continuous Power Output . . . no more than 0.02%

I. M. Distortion, 8 ohms:

at Continuous Power Output . . . no more than 0.01%
at 1 Watt Power Output no more than 0.02%

IHF Power Bandwidth, 8 ohms: 10 ~ 70000Hz

Damping Factor at 1000 Hz, 8 ohms: more than 80

Frequency Response, "NORMAL" input, 8 ohms:

at 1 Watt Power Output . . 20 ~ 100000Hz +0, -1dB

Input Sensitivity for 300 Watts Power Output:

MAIN IN 1V ± 2dB

Signal to Noise Ratio, IHF "A" Network:

MAIN (NORMAL, DIRECT) . . . better than 115dB

Signal to Noise Ratio, DIN Filter:

MAIN IN (NORMAL, DIRECT) . . better than 90dB

Channel Balance: no more than 1dB

Residual Hum and Noise, 8 ohms: . . no more than 0.4 mV

Idling Current: 50 ~ 150mA

Midpoint Voltage: 0 ± 30mV

Muting Delay Time: 2 ~ 7 seconds

GENERAL

Power Requirement:

W-TYPE AC 120V, 60Hz
E-TYPE AC 220V, 50Hz
B-TYPE AC 240V, 50Hz

Power Consumption: 800 W (1.25 KVA)

Ambient Temperature during Operation: . . . -10 ~ 30°C

Dimensions:

Width 482 mm (19 inches)

Height 182 mm (7 1/4 inches)

Depth 460 mm (18 1/8 inches)

Weight, without package: 21.5 kg (47.3 lbs)

BLOCK DIAGRAM

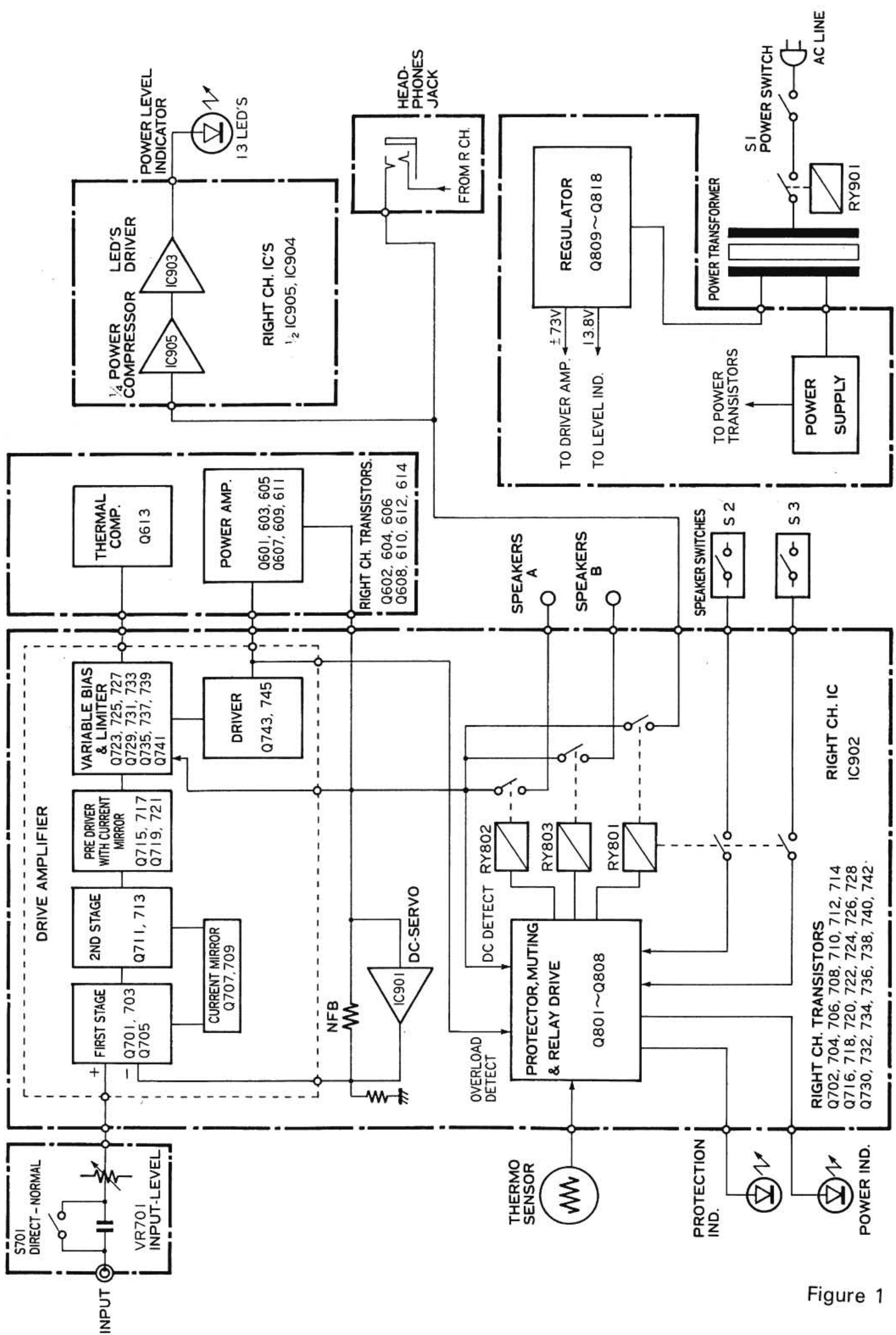


Figure 1

DISASSEMBLY

CABINET COVER REMOVAL

- a. Remove six tapping screws from the top of the unit.
- b. Remove four screws from both sides of the unit.
- c. Lift the cabinet cover away from the unit.

BOTTOM PLATE REMOVAL

- a. Remove eleven tapping screws (#1 – #11) from the bottom of the unit as shown in Photo 1.
- b. Lift the bottom plate away from the unit.

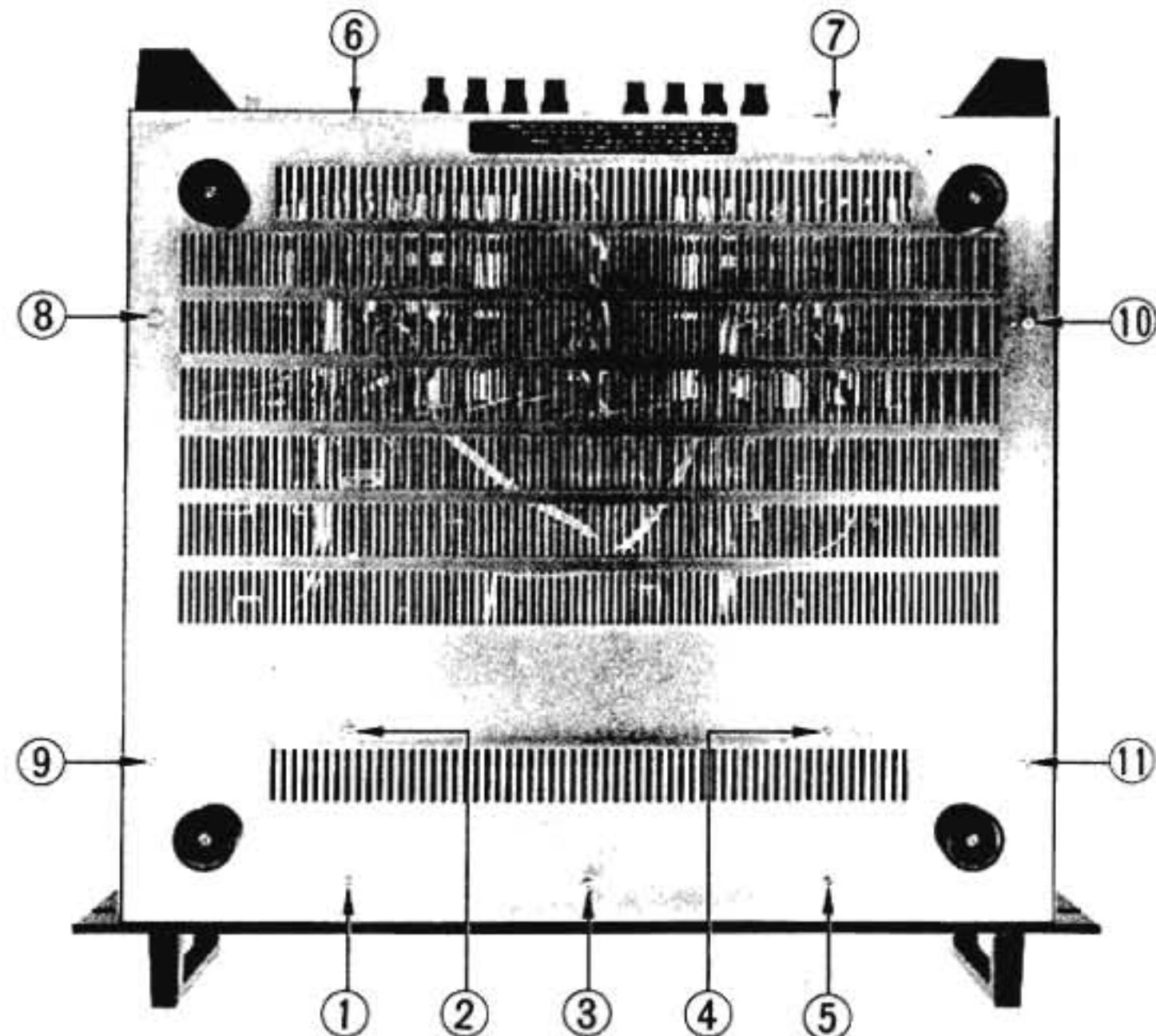


Photo 1

FRONT PANEL REMOVAL

- a. Remove four tapping screws (#1 – #4) from the left side of the unit as shown in Photo 2.
- b. Similarly remove four tapping screws from the right side of the unit.
- c. Remove the front panel away from the unit by pulling it forward.

POWER TRANSFORMER REMOVAL

- a. Remove the cabinet cover and the bottom plate.
- b. Disconnect all the cables from the power transformer.
- c. Remove four nuts (#1 – #4) from the chassis as shown in Photo 3.
- d. Lift the power transformer away from the unit.

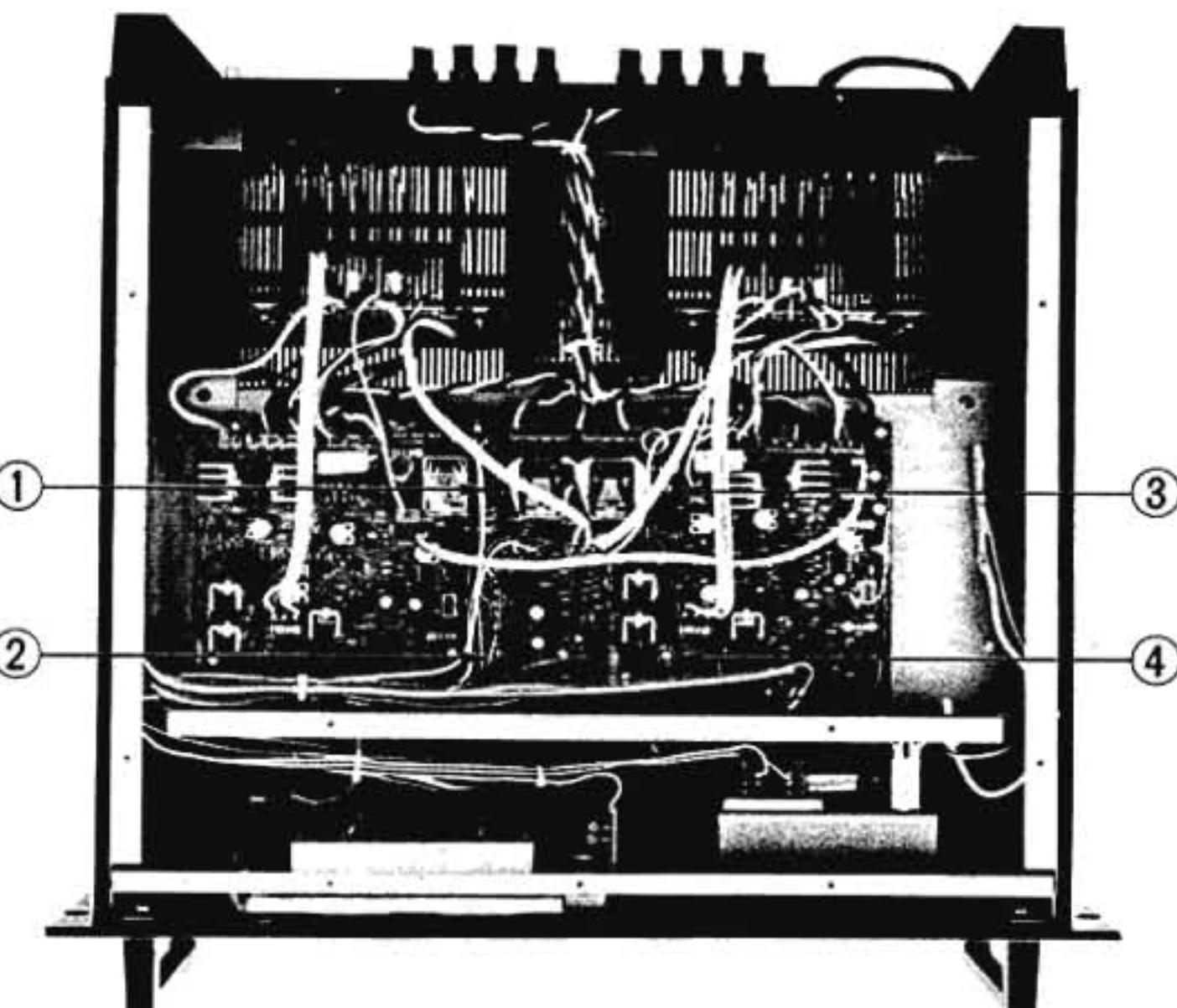


Photo 3

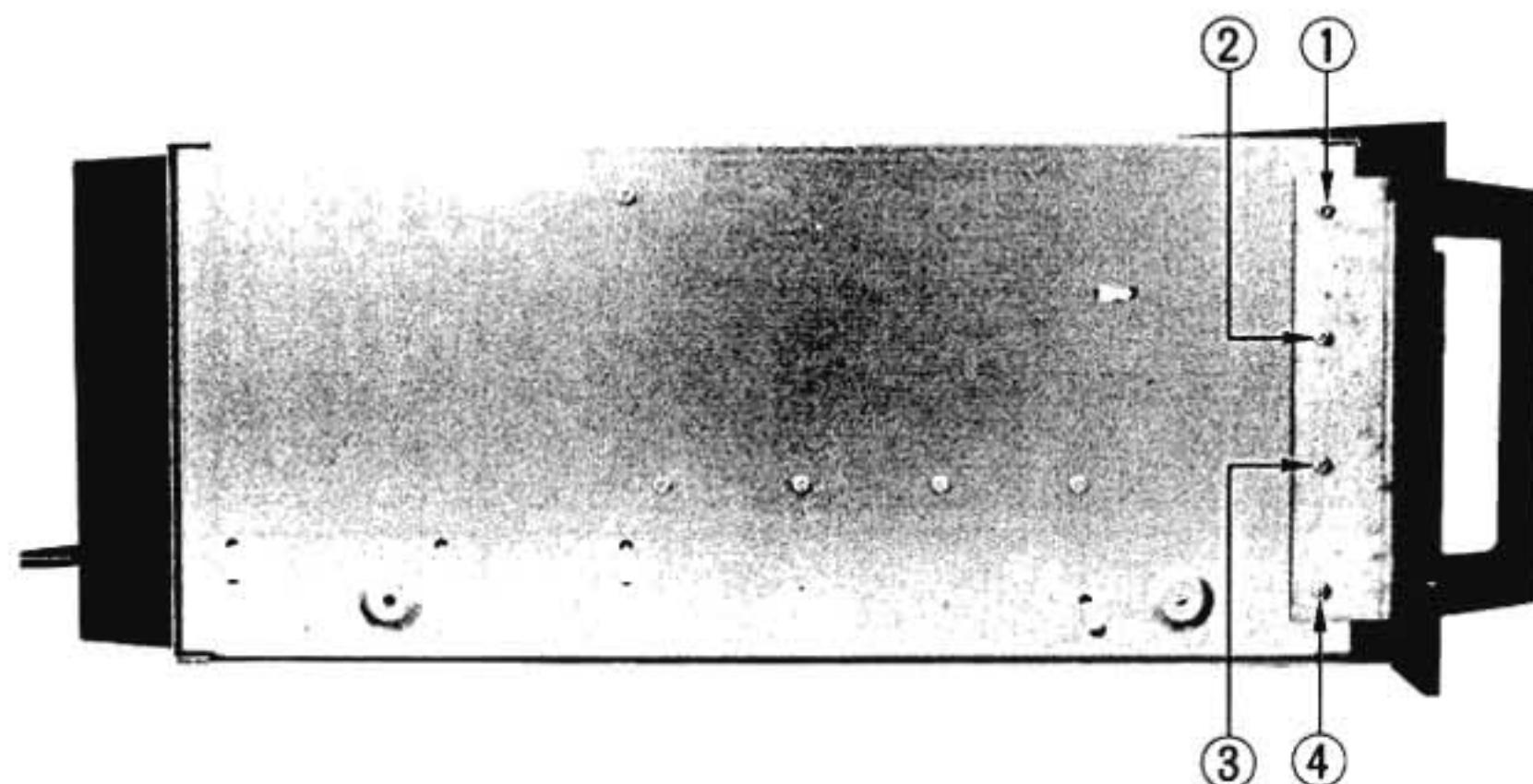


Photo 2

CIRCUIT DESCRIPTION

NIKKO's ALPHA 440, adopting latest devices such as Hi-fT power transistors, is of a design introducing a variable bias circuit (non-switching circuit), a DC servo circuit and other most advanced techniques.

For details, refer to page 2 "BLOCK DIAGRAM" and page 10 "SCHEMATIC DIAGRAM".

The following are explanations of the main circuits and devices.

1. VARIABLE BIAS CIRCUIT

Currently, in the output stage of power amplifiers are mostly used SEPP (Single Ended Push Pull) circuits. (Fig. 2).

It is generally known that the current (idle current) flowing through NPN and PNP transistors of this circuit can be classified into three large groups of operation form, class "A", class "AB" and class "B". (Fig. 3).

In class "A" operation, neither of collector currents, Q_1 and Q_2 , becomes zero nor cut off. Even when the current flowing to the load R_L is zero, a certain current is flowing through Q_1 and Q_2 , and so no crossover distortion exists theoretically.

To realize perfect class "A" operation, however, a current equal to or more than maximum output should continue to be let flow at the output stage as idle current, causing class "A" operation to prove to

be a poor efficiency system.

In class "AB" or "B" operation, the Q_1 plays the role of amplification of the plus part of the signal and Q_2 that of the minus part, no matter whether idle current is large or small.

In other words, there definitely exists a period in which, when one transistor is on, the other transistor keeps cutting off, in these operations.

Switching distortion or crossover distortion is caused at the moment of this active status turning into cut-off status or the cut-off status into the active status. Nevertheless, as these operation forms have high efficiency with small idle current, it is much easier to use class "AB" or "B" operation for high power amplification rather than class "A".

A power amplifier enjoying the merit of each of these systems — that is, practically no crossover or switching distortion being caused in class "A" operation and easier high power amplification being achieved by class "B" — has been realized by adopting the variable bias circuit.

The idea of a variable bias circuit is that in no case the output stage is allowed to be cut-off by increasing and decreasing bias voltage in corresponding with the voltage of input signal.

Fig. 4 shows the variable bias circuit adopted in ALPHA 440.

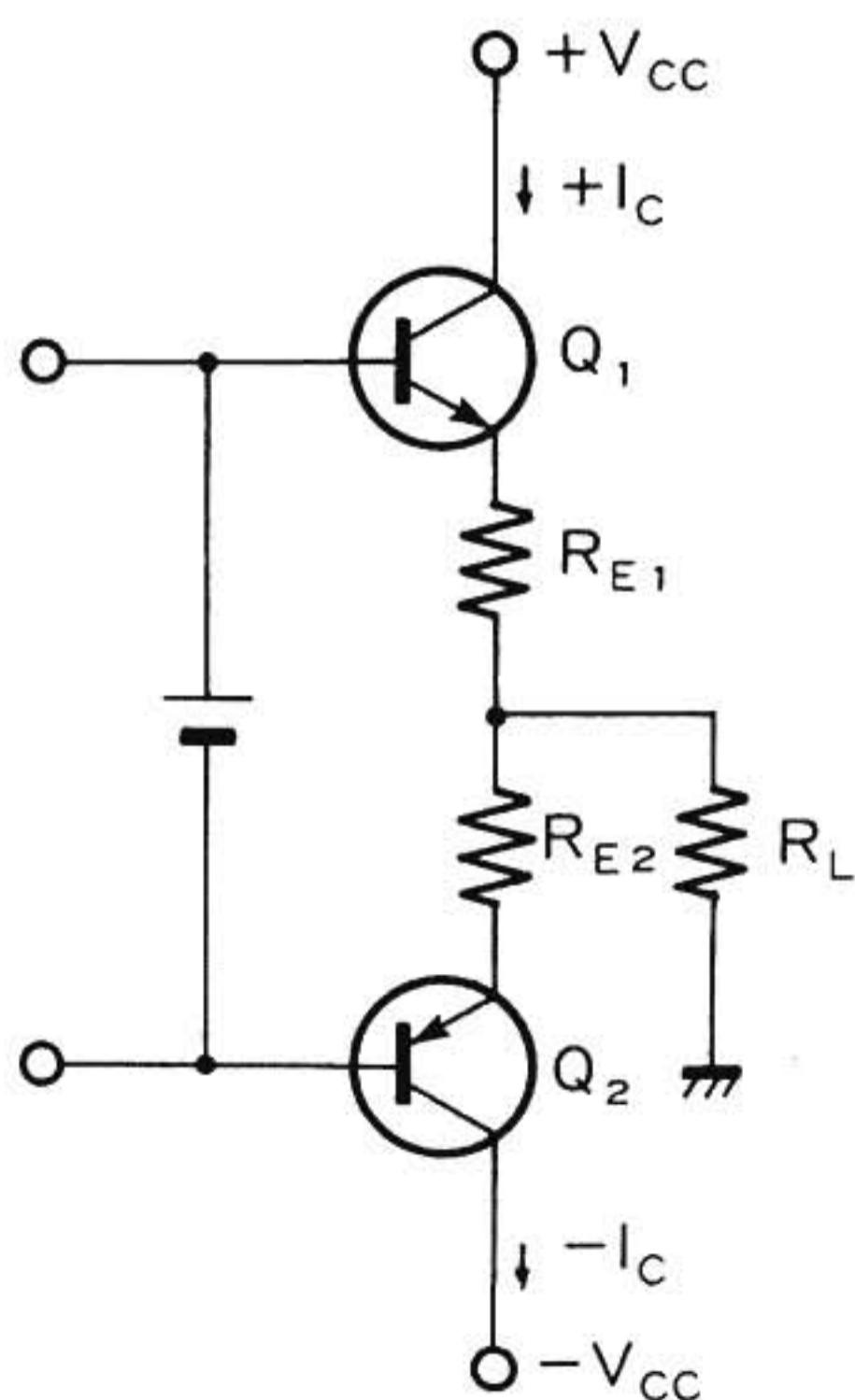


Figure 2 SEEP CIRCUIT

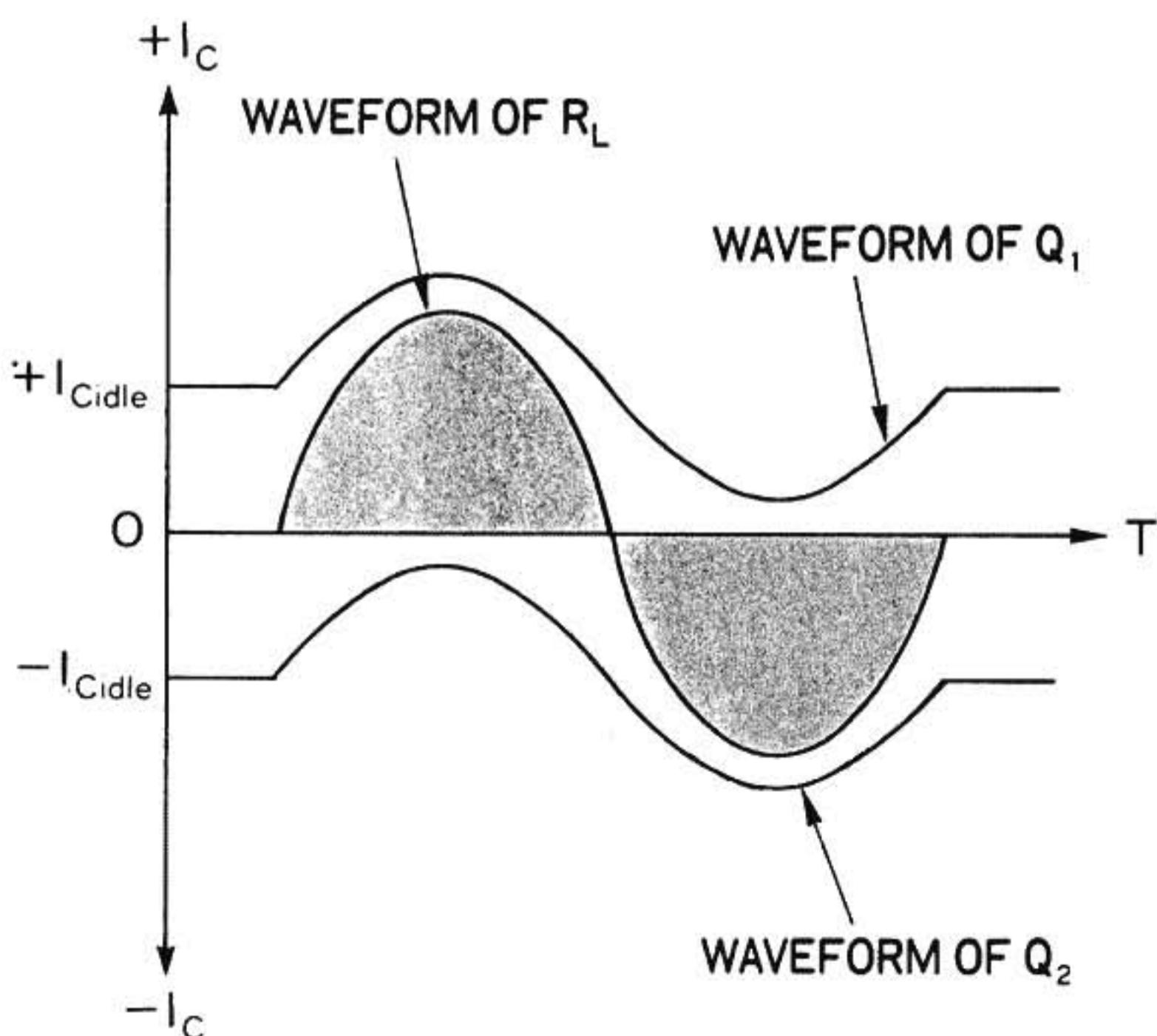


Figure 3-1 CLASS-A OPERATION

Now, suppose the plus wave (plus part) of signal has been inputted, the currents of Q_{p1} and Q_{d1} increase and the voltage at both ends of R_{E1} and R_{E3} become high, resulting in a rise in the voltage between \textcircled{A} point and OUTPUT.

At that time, the voltage at both ends of R_1 and R_3 becomes high because current flows $R_1 \rightarrow Q_1$ and $R_3 \rightarrow Q_3$, causing the potential at \textcircled{C} point to lower and the voltage of Q_5 between collector and emitter to rise.

As a result, the voltage between \textcircled{A} and \textcircled{B} rises and Q_{p2} and Q_{d2} is kept from being cut-off.

From another point of view, the voltage drops at the emitter resistors R_{E1} and R_{E3} (these resistors are indispensable to protect transistors in stabilizing bias of the output stage or at the time of abnormal current flowing) are cancelled by the drops at R_1 and R_3 , thus protecting Q_{p2} and Q_{d2} from becoming zero or anti-bias.

In the same manner, when the minus wave (minus part) of signal has been inputted, current flows $Q_2 \rightarrow R_2$ and $Q_4 \rightarrow R_4$, resulting in a rise of V_{CE} at Q_6 , thus protecting Q_{p1} and Q_{d1} from being cut-off.

2. DC SERVO CIRCUIT

DC amplification is the most advanced form adopted for audio amplifiers as there is no phase lag over all the range from DC to audio frequency.

However, in a perfect DC amplifier (which is an amplifier having no coupling capacitors in its input part and NFB loop), a DC drift is caused in case a direct current is inputted or when the DC balance between each element has been lost due to temperature rise

inside the amplifier. The DC servo circuit is to suppress such a drift and realize a more stabilized amplifier.

The principle of a DC servo circuit is something like that of a comparator, in which changes in DC current between the output point and the ground is detected and drifts of the amplifier is controlled with their results used as the output of the servo circuit.

The basic elements are an integrating circuit composed of C_1 and R_1 , an operational amplifier and a mirror integrator composed of C_2 and R_2 . (Fig. 5).

Now, suppose a drift Δe_o has been caused at the output of the power amplifier, a potential with the same phase Δe_f is outputted at the output of the operational amplifier.

On the other hand, the initial stage of the power amplifier is a differential amplifier. When Δe_f is inputted at its inverting input, the potential at the non-inverting input Δe_i changes in the opposite direction of Δe_f , resulting in a decrease of drift at the output of the power amplifier.

The DC servo circuit has a specific frequency characteristic. In the range of DC and ultra low frequency, gain of the power amplifier is kept at one over several tens of decibel, and in the audio frequency band, amplification at a certain gain can be made in the same manner as ordinary power amplifier.

The frequency on which the DC servo circuit starts to have effects is determined by the four elements, C_1 , R_1 , C_2 and R_2 .

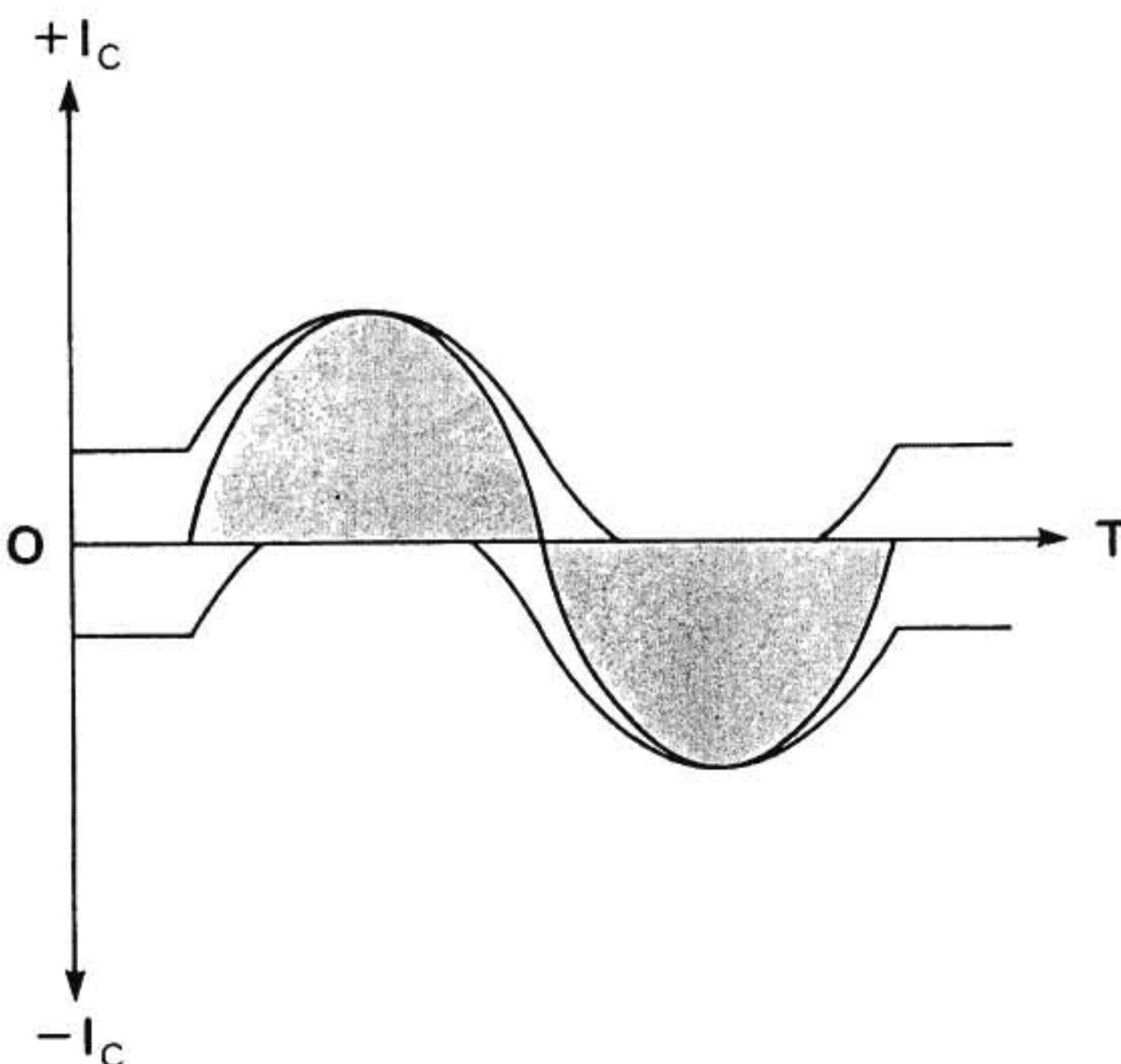


Figure 3-2 CLASS-AB OPERATION

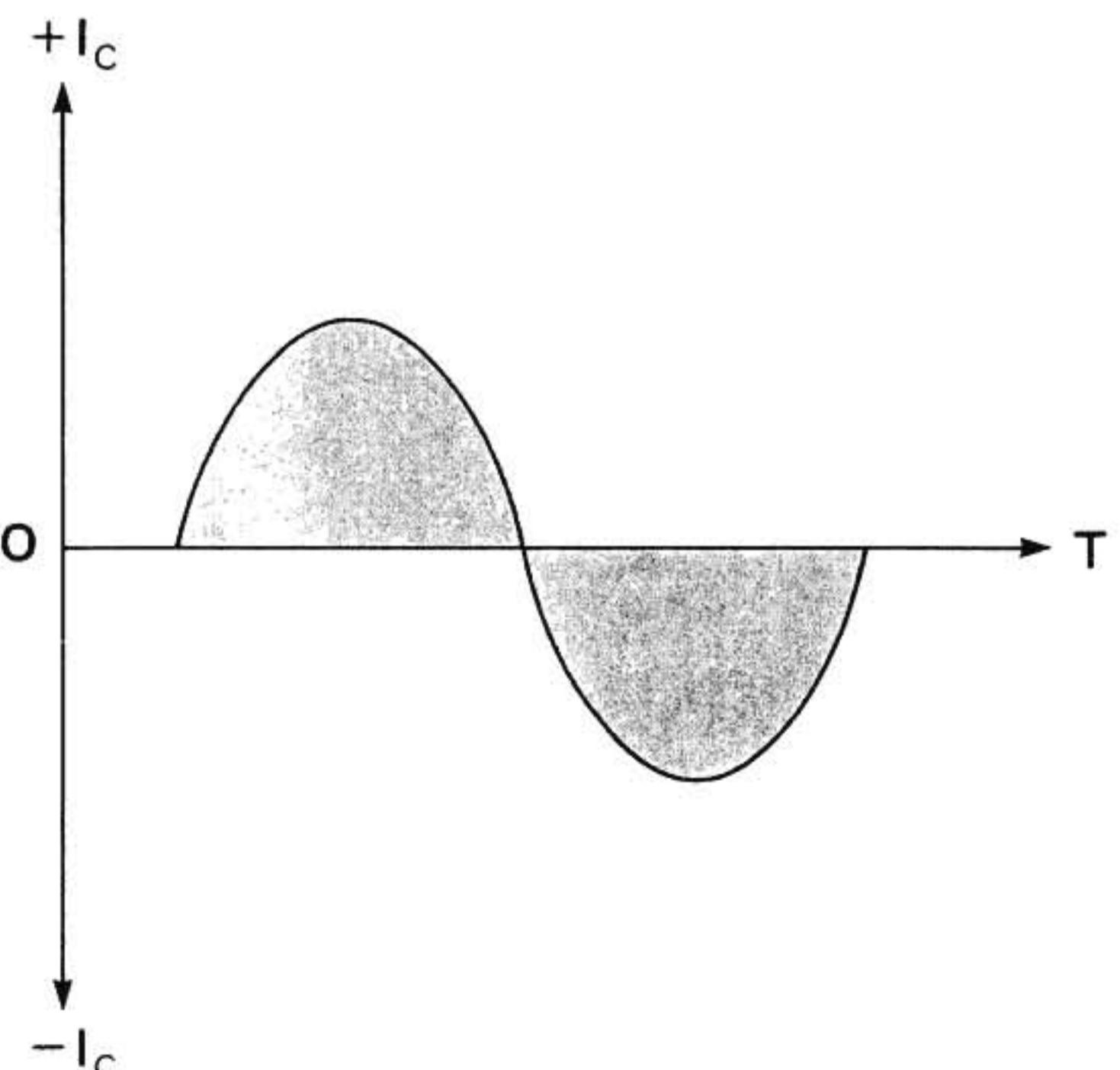


Figure 3-3 CLASS-B OPERATION

3. Hi-FT POWER TRANSISTORS

For details characteristics, refer to "SEMICONDUCTOR DATA" at the end of this manual.

The power transistors employed in ALPHA 440 realize an f_T (Current Gain-bandwidth Product) of 80 MHz with NPN type and 60 MHz with PNP type (each being a typical value) in spite of its high P_c (Collector Power Dissipation) such as 150 W (The value when $T_c = 25^\circ\text{C}$). Compared with conventional transistors with a P_c of 150 W where f_T was around 10 MHz at maximum, the high speed attained by these Hi-FT power transistors is remarkable.

Such high f_T has been realized specially by the inside construction of these transistors which is greatly different from that of conventional ones — the multi-emitter construction.

In this construction, the emitter inside the transistor is divided into many units and emitter resistors with small resistance are inserted to each unit, resulting in a parallel connection.

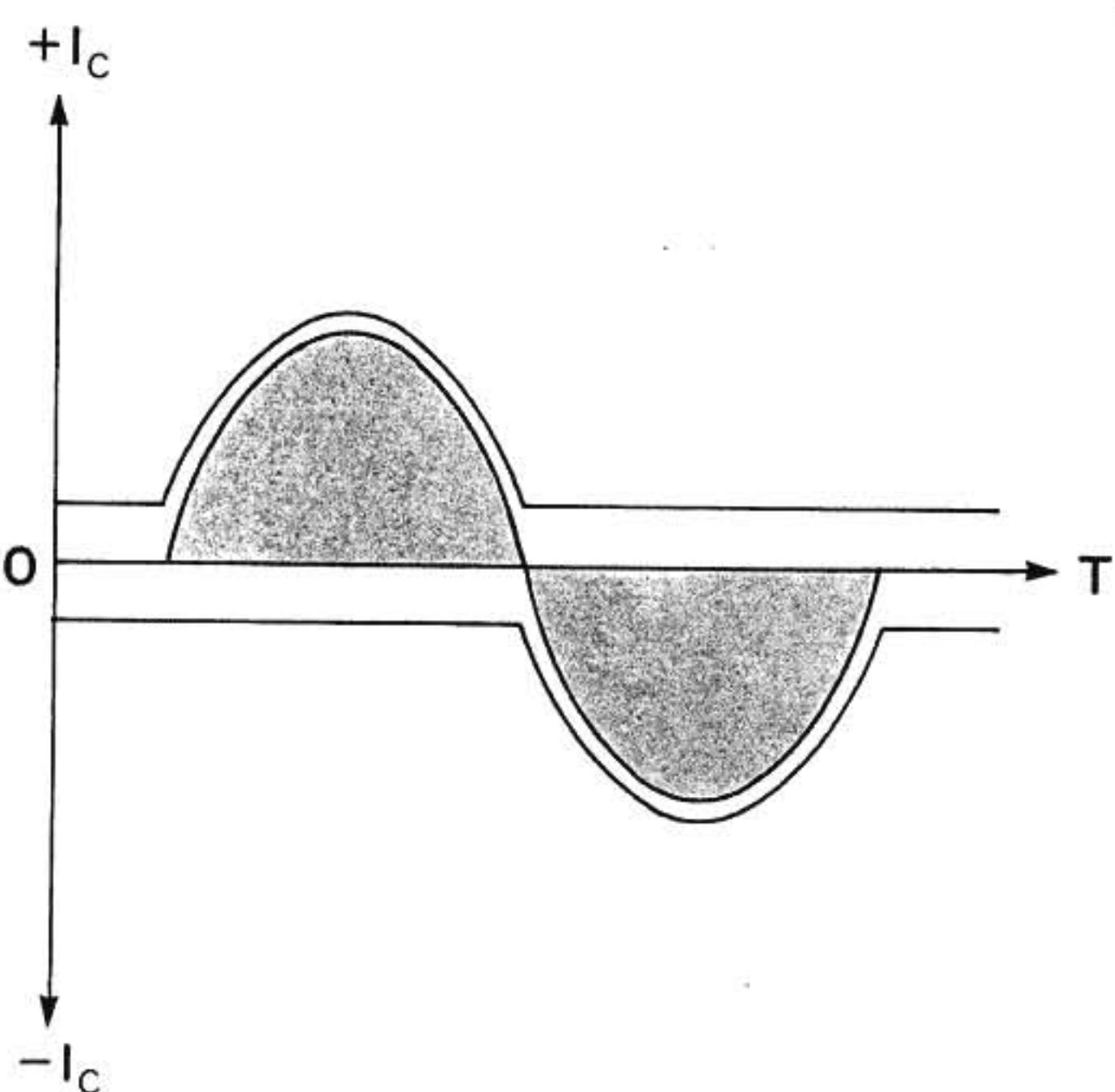


Figure 3-4 OPERATION OF BARIAVLE BIAS

This equivalently means that many small signal transistors with high f_T and switching speed are parallelly connected, which has made it possible to realize such a high power characteristic while maintaining high switching speed.

Thanks to such construction as mentioned above, these power transistors are excellent in linearity of its h_{fe} .

Furthermore, as dissipation is dispersed equally to each emitter due to the emitter-divided construction, they have another feature of being strong against breakdown as compared with conventional power transistors.

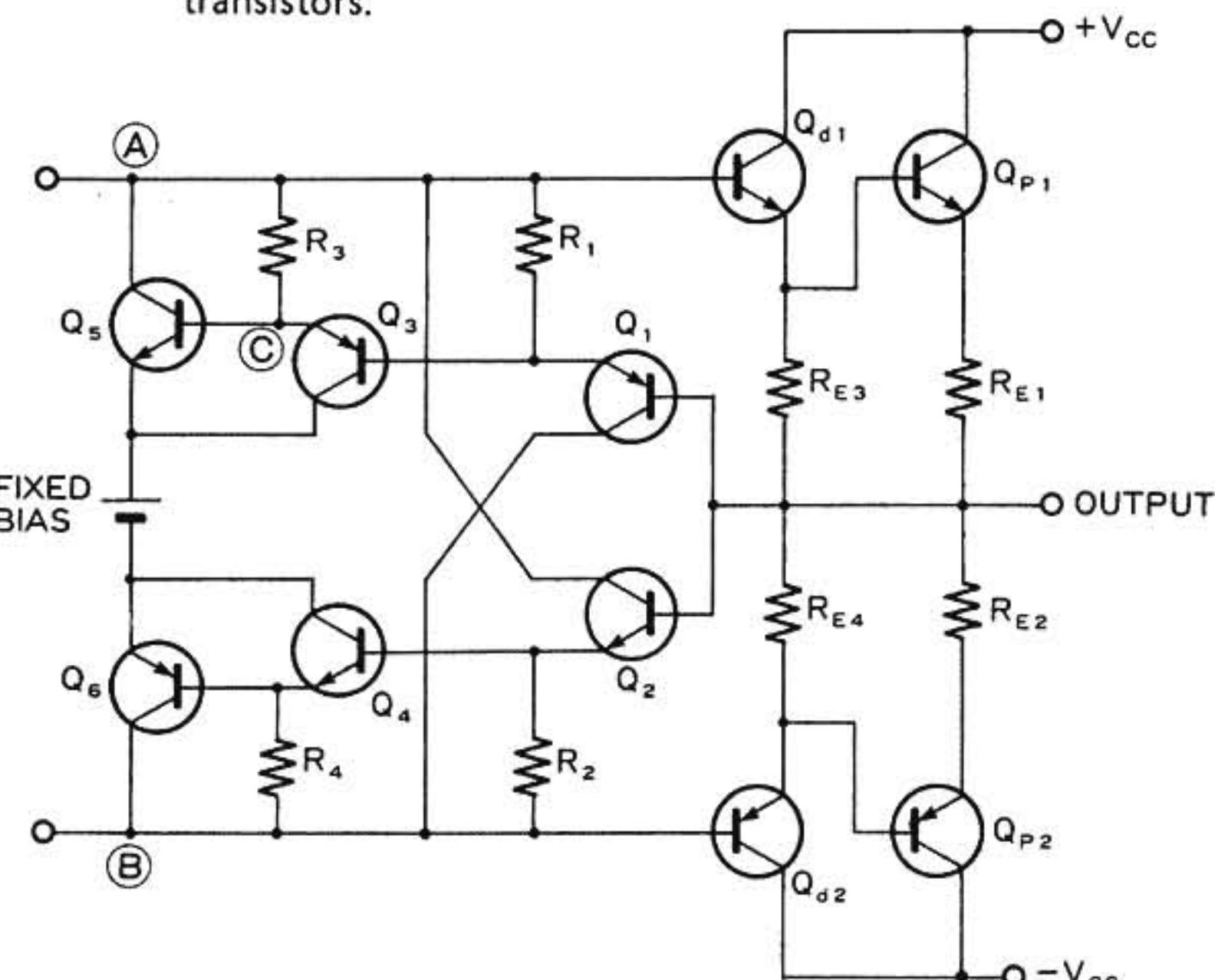


Figure 4 VARIABLE-BIAS CIRCUIT

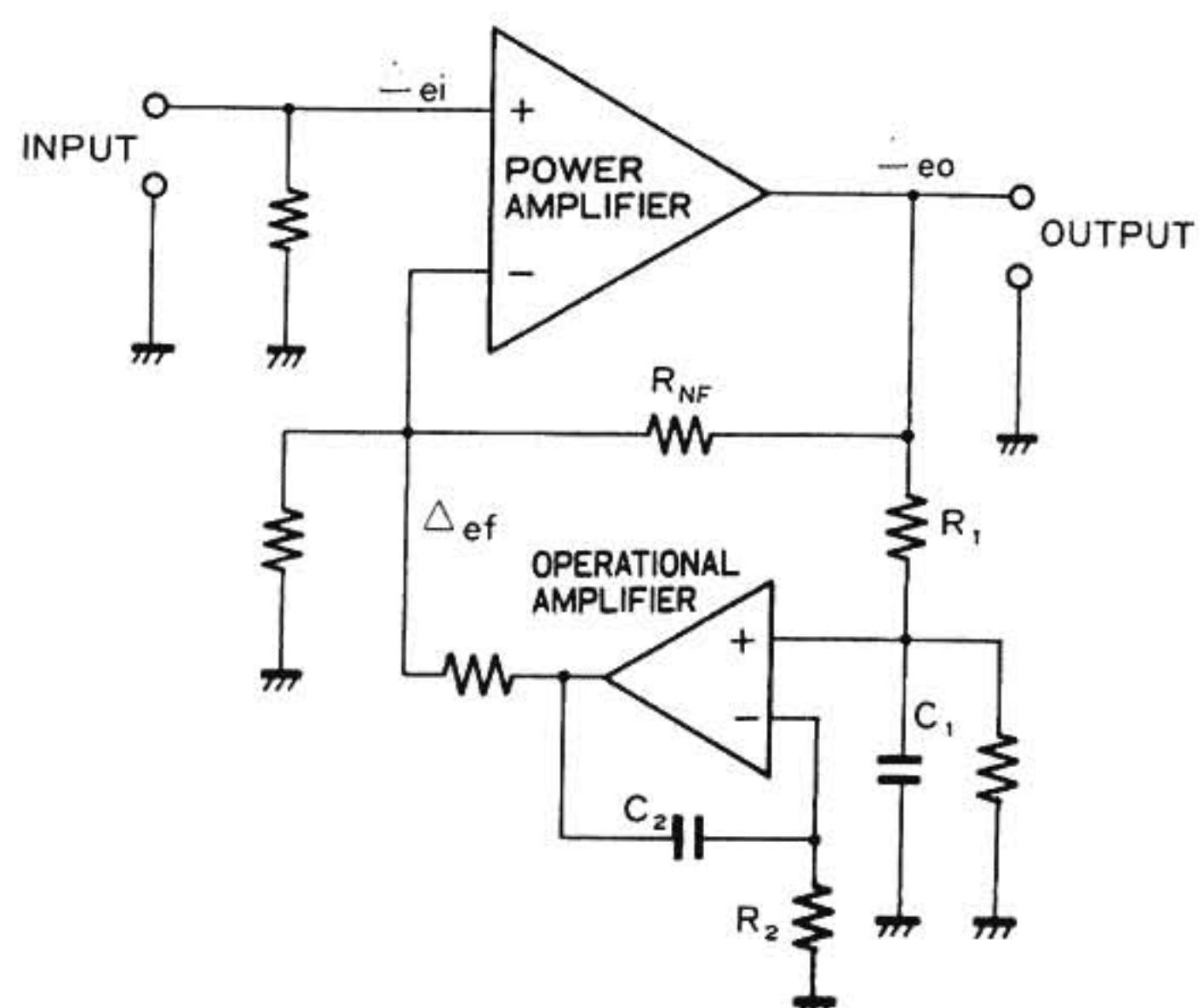


Figure 5 DC-SERVO CIRCUIT

ALIGNMENT

ALIGNMENT PRECAUTIONS

1. As the ALPHA 440 is a power amplifier with large output power, it consumes much electrical power and a great amount of current flows in the power source line of the primary side. Therefore, in the case when it is connected to the source by an extension cord, the size of the extension cord should be equal or larger than that of the power source cord of the ALPHA 440. Otherwise, the voltage might be reduced or the extension cord might generate excessive heat because of the resistance which the cord has, then not only can proper alignment be done, but also it is very dangerous.
2. If the power sources are supplied to the ALPHA 440 and the instruments by branching off from one cord, the voltage is sometimes dropped down and the stability of the instruments goes down.
The ALPHA 440 and the instruments should be connected to the power sources by using independent cords. The ALPHA 440 must take the power source from AC outlet of the wall side.
3. As there are many parts which hold high voltages in the circuit and the parts inside of the ALPHA 440, be careful not to receive an electric shock. In the case of connecting and taking off the instruments, you must turn off the power switch of the ALPHA 440 before getting on the work.
4. When the circuit happens to be shorted by the drivers or test probes used for alignment through mistake, the circuit and the parts will be damaged. As the damage is larger than that of ordinary amplifiers and receivers, close attention is needed. It is advised that the screw driver, excluding the top part, should be wrapped with insulation tape or a driver made of plastic or some kind of insulating material should be used.
5. As the dummy load resistor generates heat while alignment, it gets very hot and you may be burnt if you touch it with bare hands. It is better if you can put the dummy load resistor in a place away from being touched, but the wire between the dummy load resistor and the amplifier should not be long. Conceive some method, like putting the dummy load resistor in a well ventilated box. Further, as more than 10 A current might flow in the wire connecting the dummy load resistor and the amplifier, at least larger than AWG #18 thick wire should be used.
6. The slide switch near the "INPUT LEVEL" volume on the rear panel of the amplifier is to be set in the "NORMAL" position. All the adjustments in the following should be done after the slide switch is set in the "NORMAL" position.

TEST EQUIPMENT

Allow a minimum of 10 minutes warm-up for test equipment.

Maintain rated line voltage.

Audio Frequency Generator
Distortion Meter
Oscilloscope
AC Voltmeter
DC Voltmeter
2-Dummy Load Resistors, 8 ohms, 500 W
2-Dummy Load Resistors, 4 ohms, 500 W

All the semi fixed resistors of the MAIN AMP PCB are set around the center position temporarily. (HVR701 ~ 706, HVR901 and HVR902)

DC BALANCE ADJUSTMENT

1. Connect 8 ohms dummy load resistors to the left and right channel speaker terminals.
2. Turn the "INPUT LEVEL" volume controls down to the fully counter clockwise, and set it to "MIN".
3. Turning on the power switch of the ALPHA 440.
4. Adjust the semi-fixed resistor R901 (left channel) or R902 (right channel) for a 0 ± 5 mV DC voltmeter reading.
5. Turning on the power switch, till the DC balance settled down. This takes about 10 minites. So after adjustment, keep the power switch for 10 minites, then make sure the DC balance again.
6. Turning off the power switch. Remove the DC voltmeter and 8 ohms dummy load resistors.

LIMITER CIRCUIT ADJUSTMENT

NOTE: See illustration, Figure 6, for test equipment hook-up.

1. Connect 4 ohms dummy load resistors to the left and right channel speaker terminals.
2. Connect the AC voltmeter, distortion meter and the oscilloscope to the left (right) channel speaker terminals. Connect the generator to left (right) channel input terminal.
3. Turning on the power switch of the ALPHA 440.
4. Turn the "INPUT LEVEL" volume control fully clockwise, and set it to "MAX".
5. Set the frequency of the generator to 1KHz. Adjust the output level of the generator so as to make the output power 260 W. (32.5 V AC voltmeter reading.)
6. Adjust the semi-fixed resistors HVR703 ~ HVR706 so that the upper and the lower side peaks of the output waveform begin to clip. (HVR703 and 705

are for the left channel, HVR704 and 706 for the right.)

7. Turning off the power switch. Remove 4 ohms dummy load resistors.

IDLING CURRENT ADJUSTMENT

1. Connect the 8 ohms dummy load resistors to the left and right channel speaker terminals.

Connect the DC voltmeter across the wiring terminals No. 16 and 17 (left channel) or No. 35 and 36 (right channel) on the MAIN AMP PCB.

2. Turning on the power switch of the ALPHA 440. Adjust the semi fixed resistor HVR701 (left channel) or HVR702 (right channel) so that the DC voltmeter indicates $18 \text{ mV} \pm 1 \text{ mV}$.
3. Turn off the power switch of the ALPHA 440 and remove the DC voltmeter and 8 ohms dummy load registers.

POWER LEVEL INDICATOR ADJUSTMENT

NOTE: See illustration, Figure 6, for test equipment hook-up.

1. Connect 8 ohms dummy load resistors to the left and right channel speaker terminals.
2. Connect the AC voltmeter, distortion meter and the oscilloscope to the left (right) channel speaker terminals. Connect the generator to left (right) channel input terminal.
3. Turning on the power switch of the ALPHA 440.
4. Turn the "INPUT LEVEL" volume control fully clockwise, and set it to "MAX".
5. Set the frequency of the generator to 1 KHz. Adjust the output level of the generator so as to make the output power 170 W. (37 V AC voltmeter reading.)
6. Adjust the semi-fixed resistors HVR921 (left channel) and HVR922 (right channel) of the LEVEL INDICATOR PCB so that the LED of "200 W" dimly lights up.
7. Turning off the power switch of the ALPHA 440.
8. Remove all test equipment.

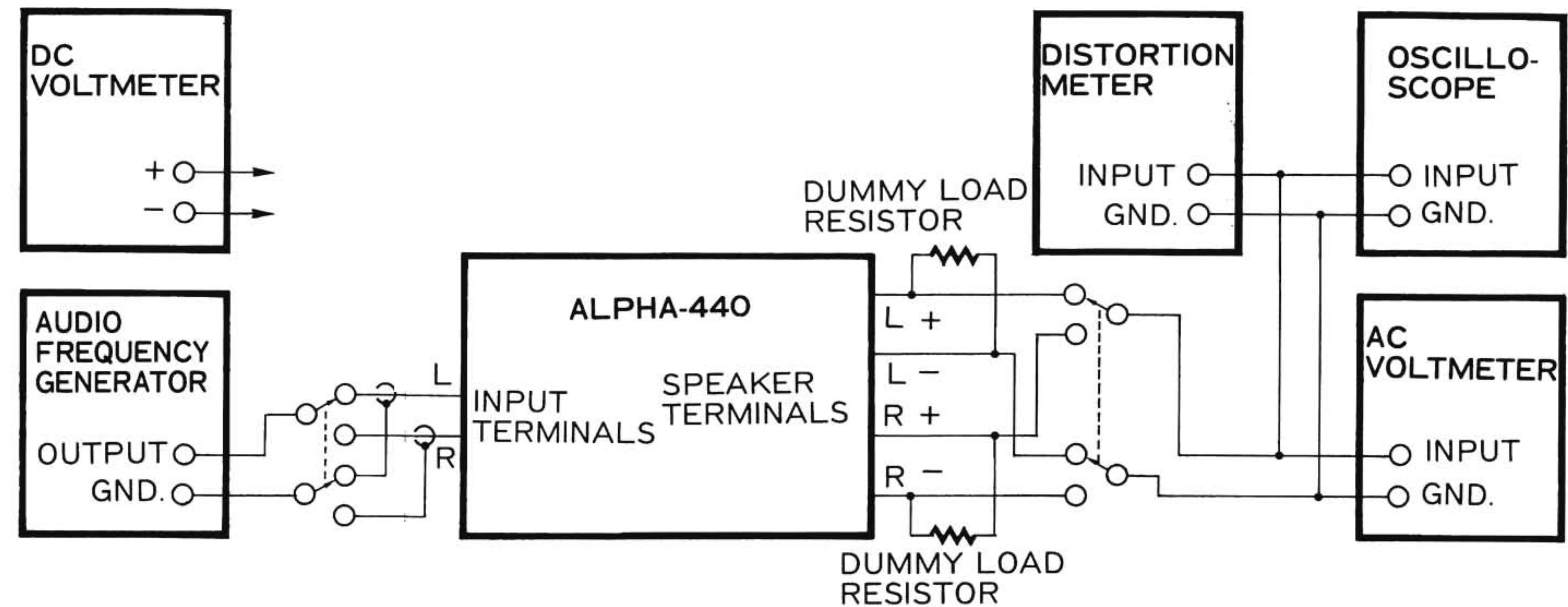


Figure 6 TEST EQUIPMENT HOOK-UP

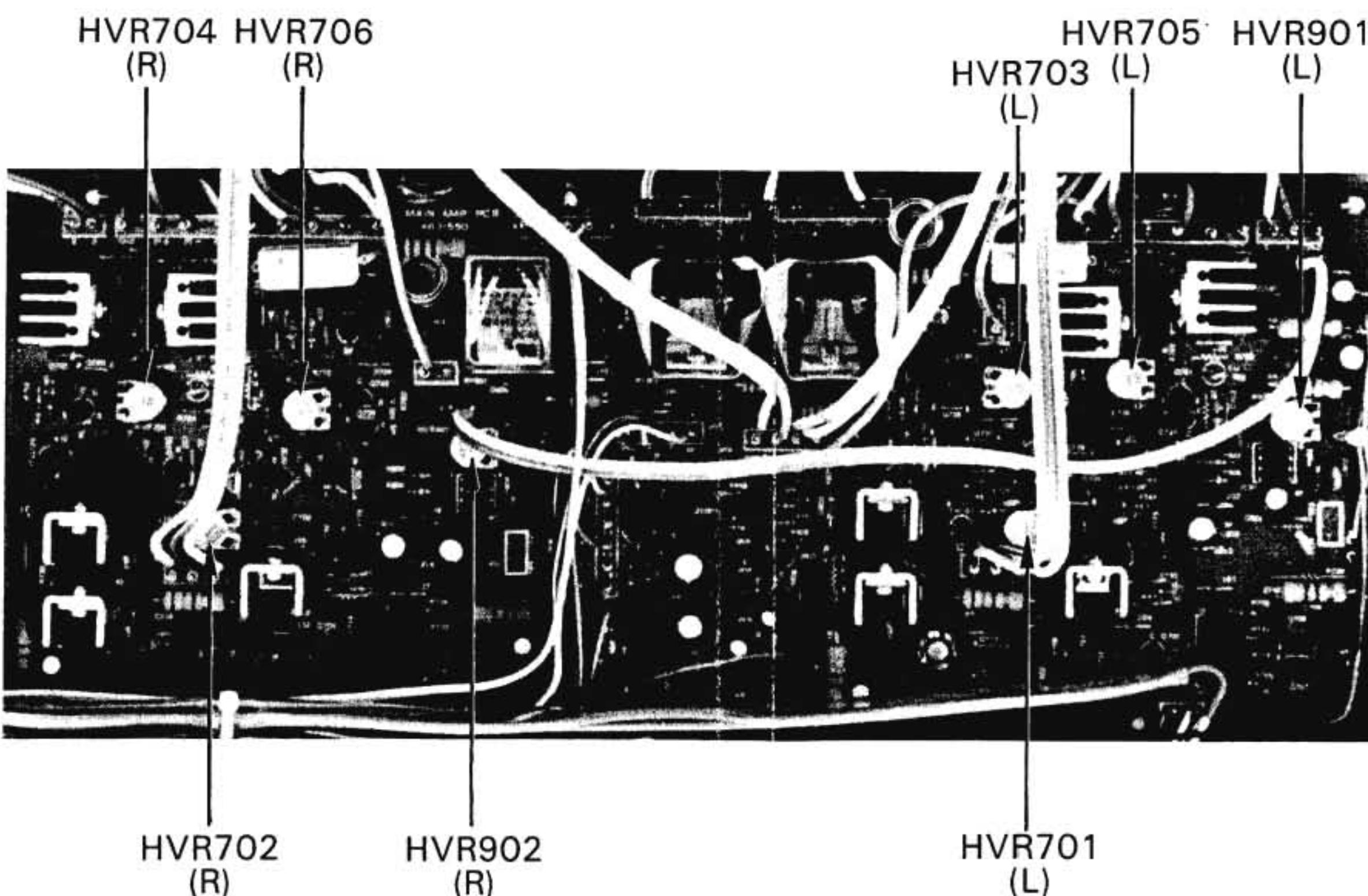


Photo 4 ADJUSTMENT POINTS

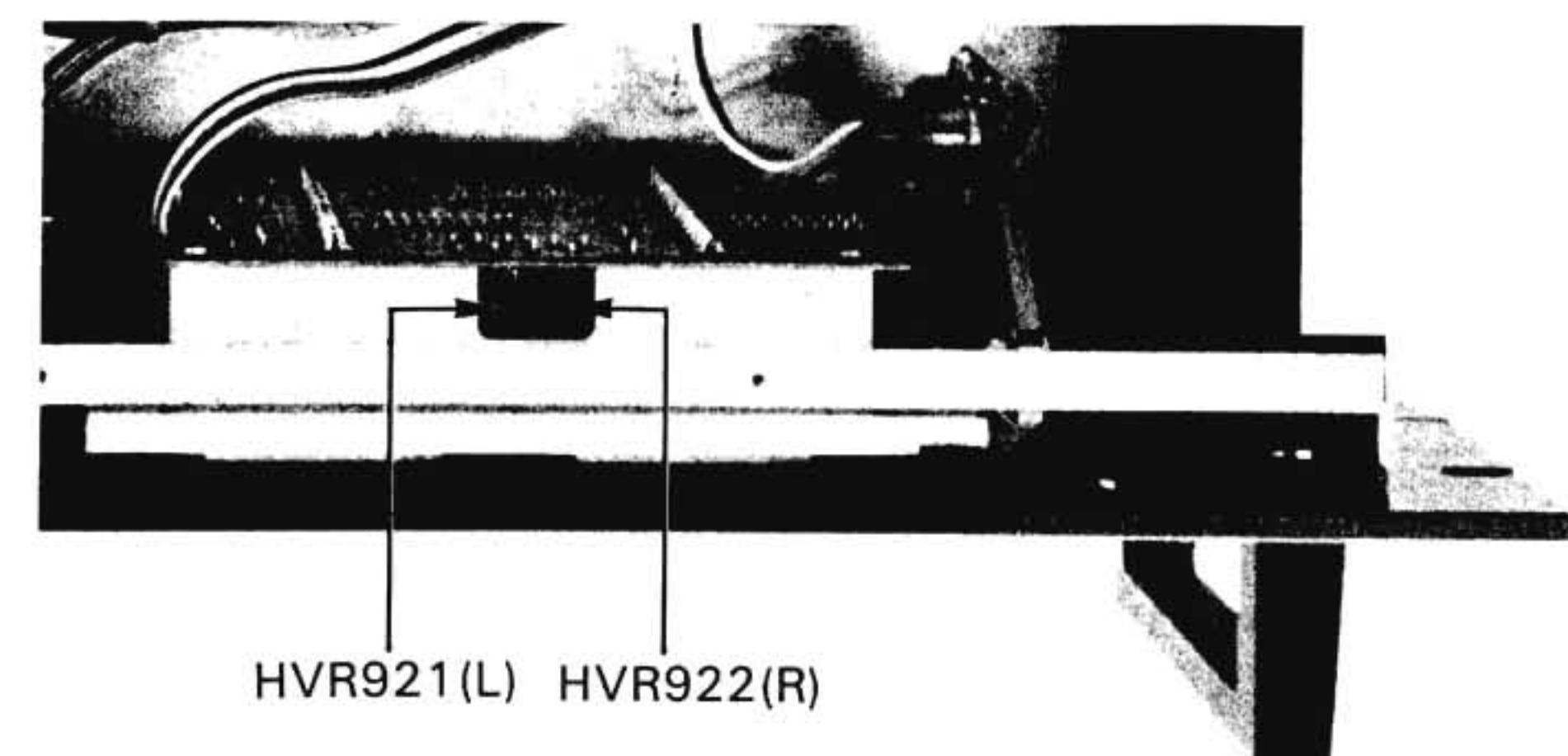
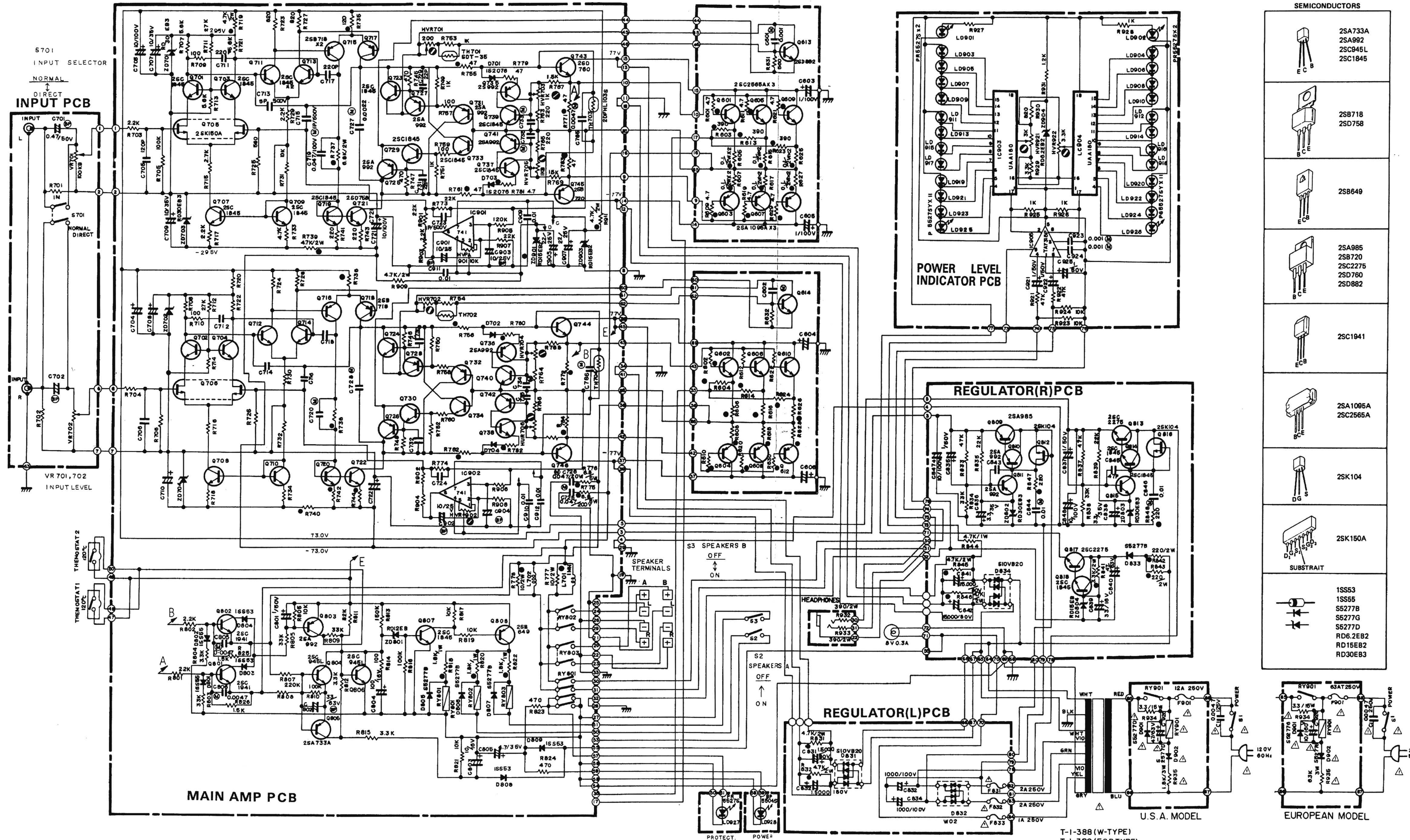


Photo 5 ADJUSTMENT POINTS

SCHEMATIC DIAGRAM



NOTES:

1. SCHEMATIC IS SUBJECT TO CHANGE WITHOUT NOTICE.
2. RESISTANCE VALUES ARE IN OHMS.
 $K = 1,000$; $M = 1,000,000$
3. CAPACITANCE VALUES 1.0 AND ABOVE ARE IN pF OR μF ($P = pF$, $M = \mu F$), LESS THAN 1.0 ARE IN μF . (ELECTROLYTIC CAPACITANCE VALUES ARE IN $\mu F/WV$)
4. VOLTAGES ARE MEASURED TO CHASSIS GROUND WITH A "DC VOLTmeter".


SCHEMATIC SYMBOLS:

- (C) POLYESTER FILM CAPACITOR
- (C_b) BIPOLAR CAPACITOR
- (R) NONFLAMMABLE RESISTOR

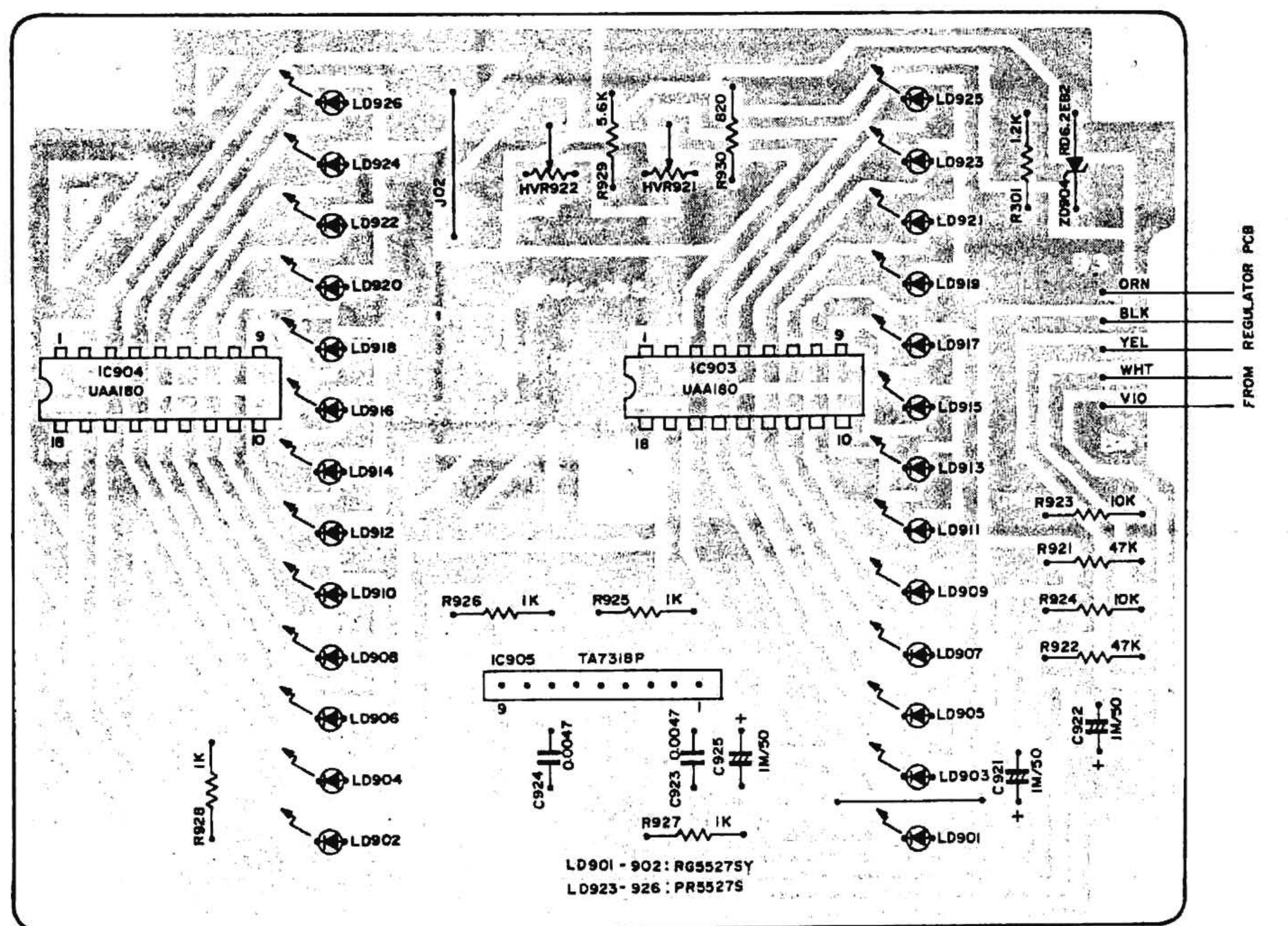
WARNING:
△ INDICATES SAFETY CRITICAL COMPONENTS.
FOR CONTINUED SAFETY, REPLACE SAFETY CRITICAL COMPONENTS ONLY WITH MANUFACTURER'S RECOMMENDED PARTS.

Figure 7

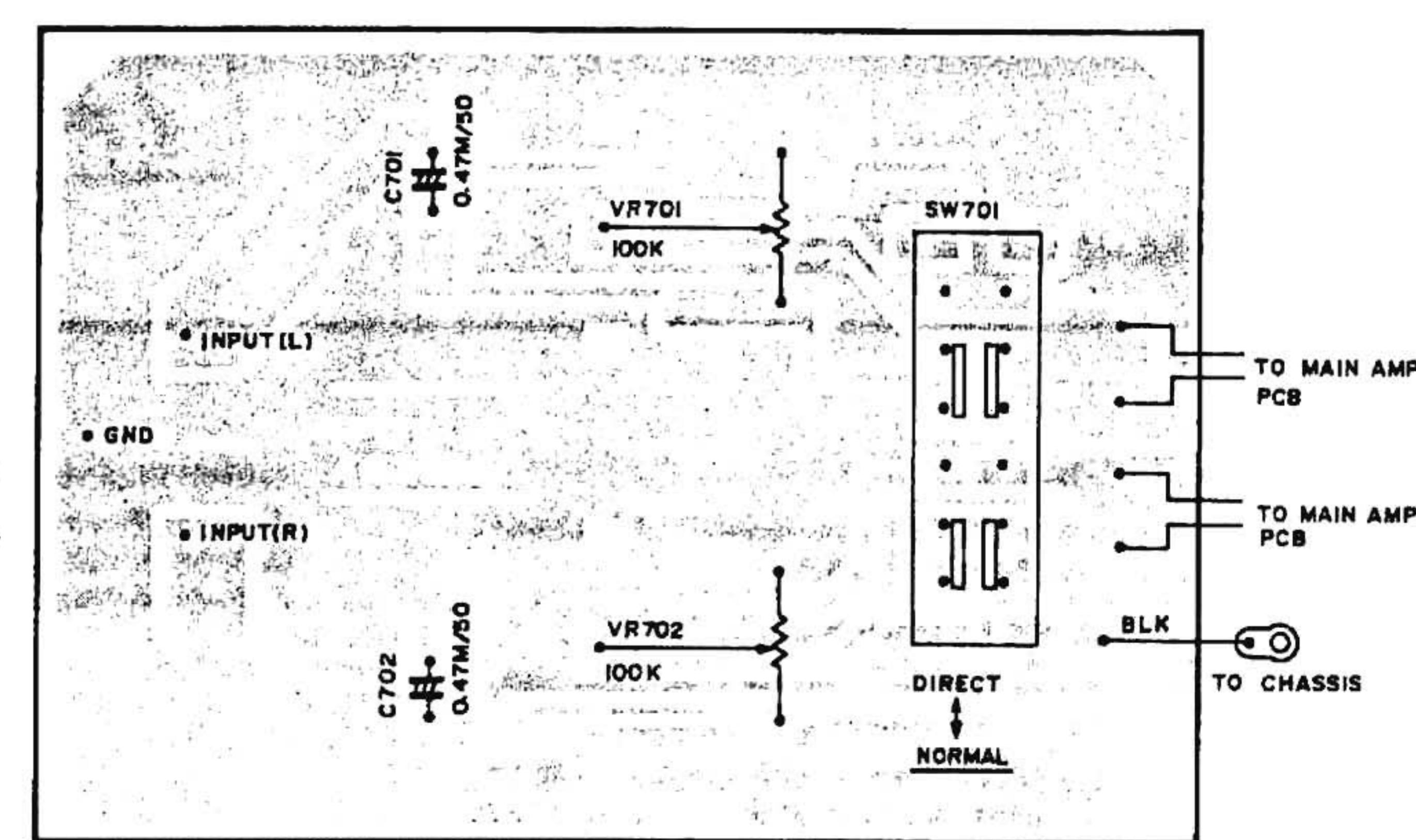
P. C. BOARD (CONDUCTIVE SIDE VIEW) Figure 8



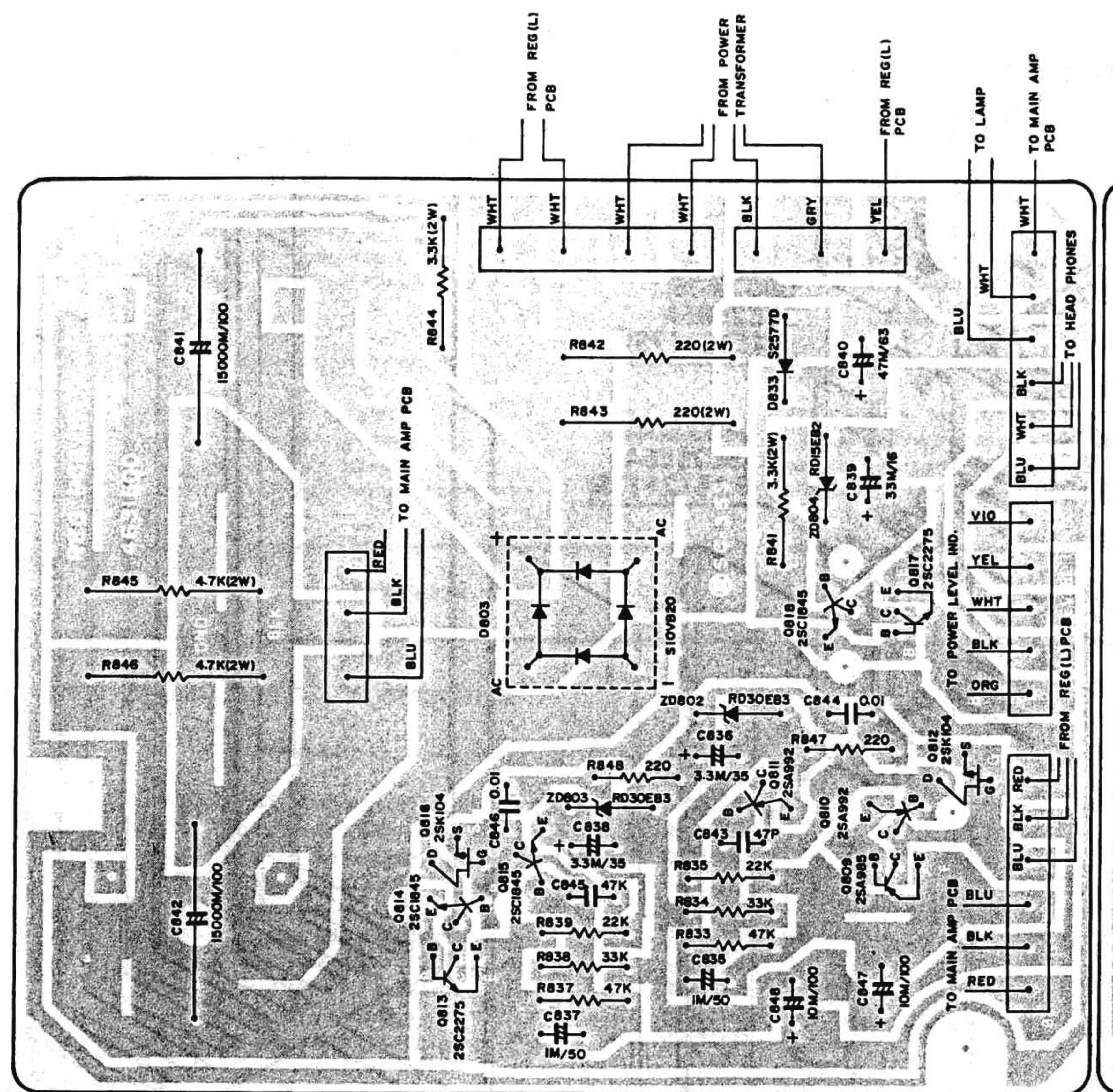
MAIN AMP PCB



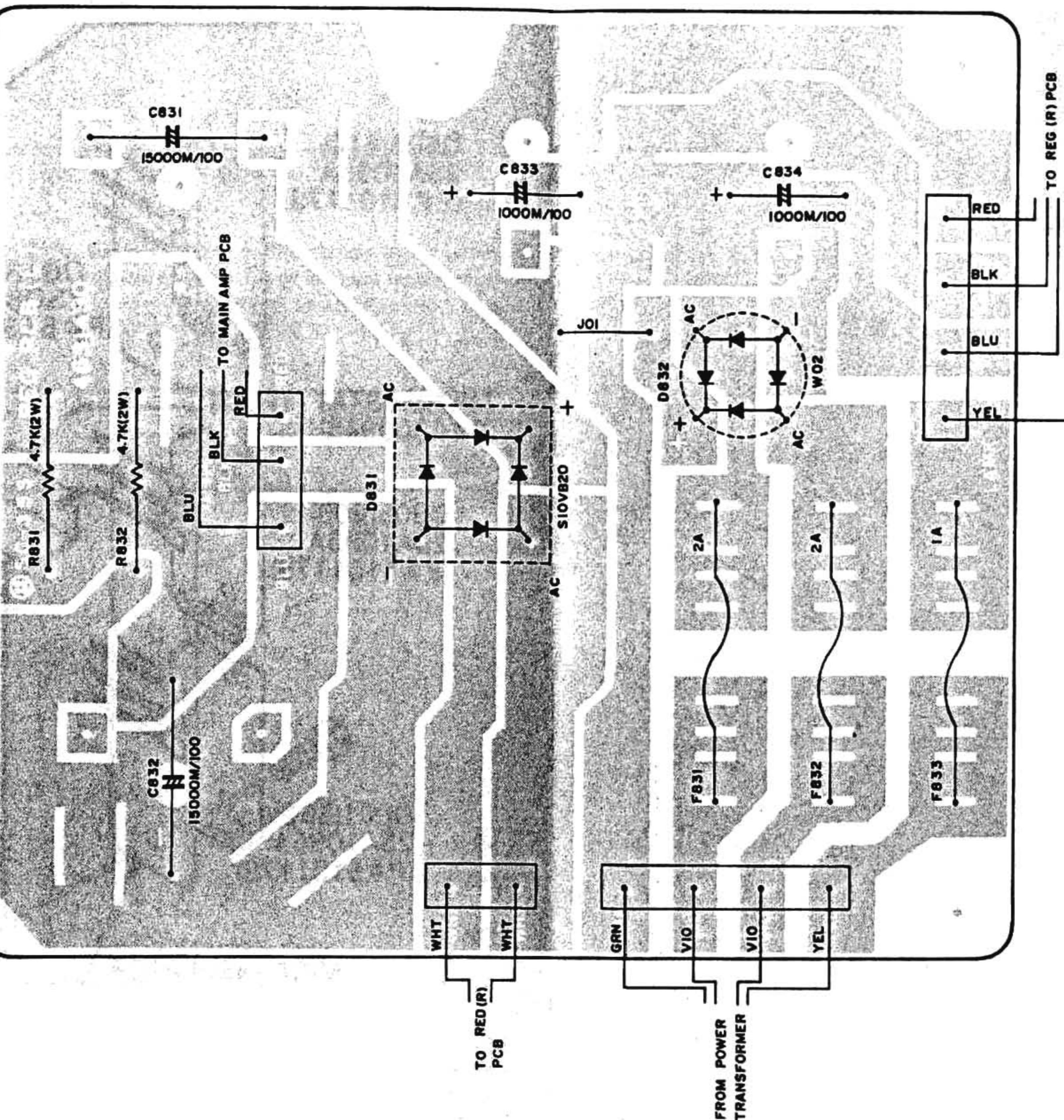
POWER LEVEL IND. PCB



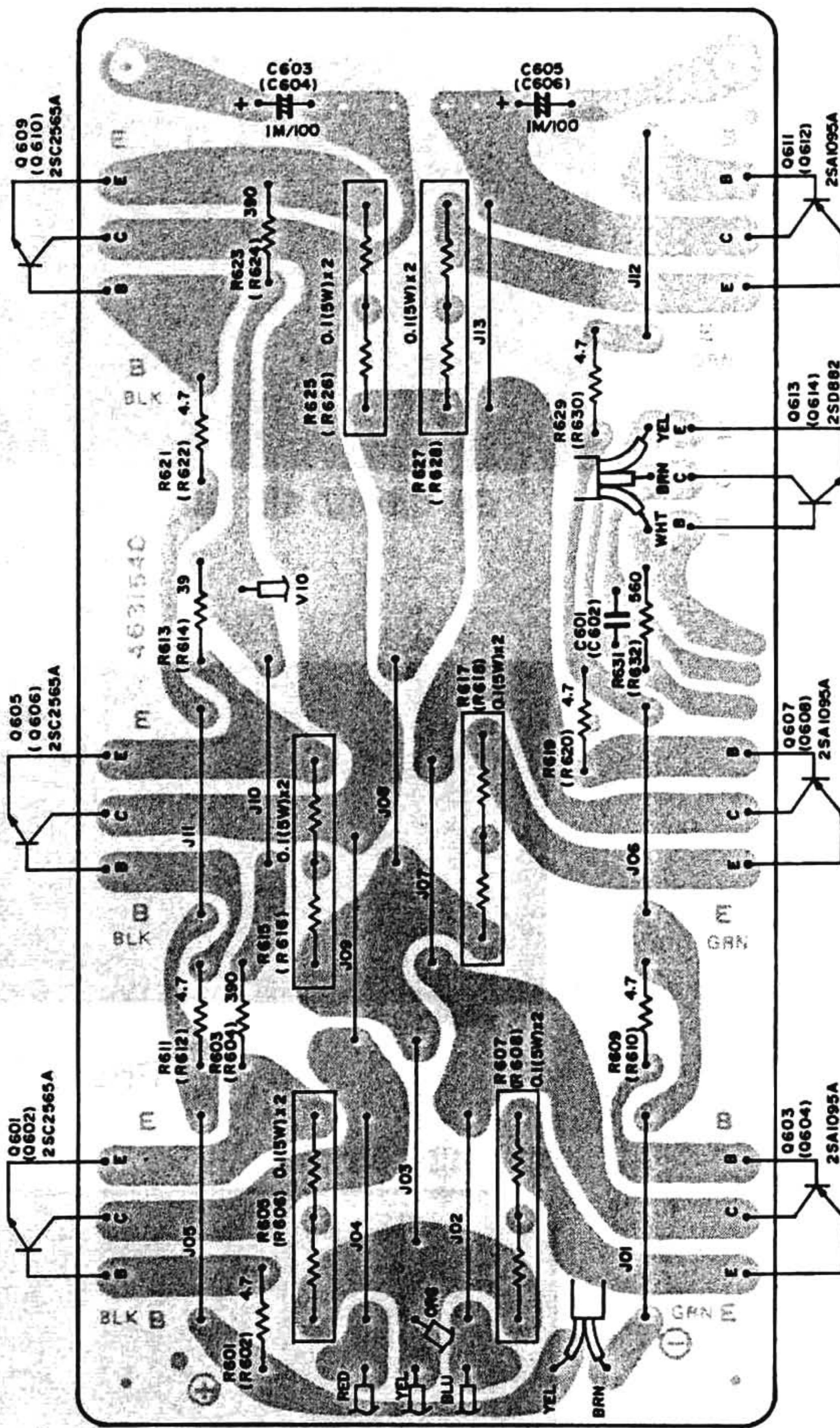
INPUT PCB



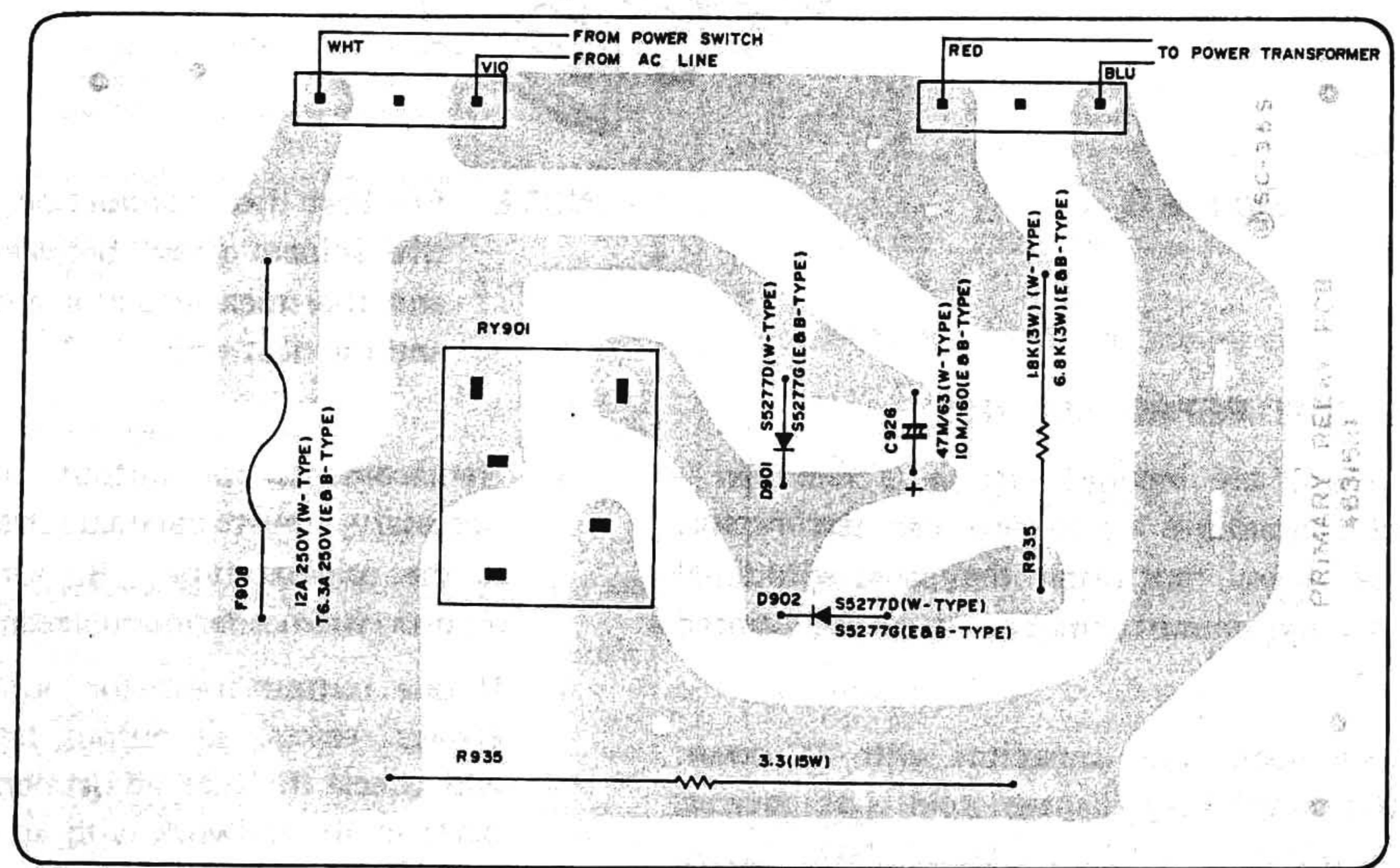
REGULATOR (R) PCB



REGULATOR(L) PCB



POWER TRANSISTORS PCB



PRIMARY RELAY PCB

PARTS LOCATION

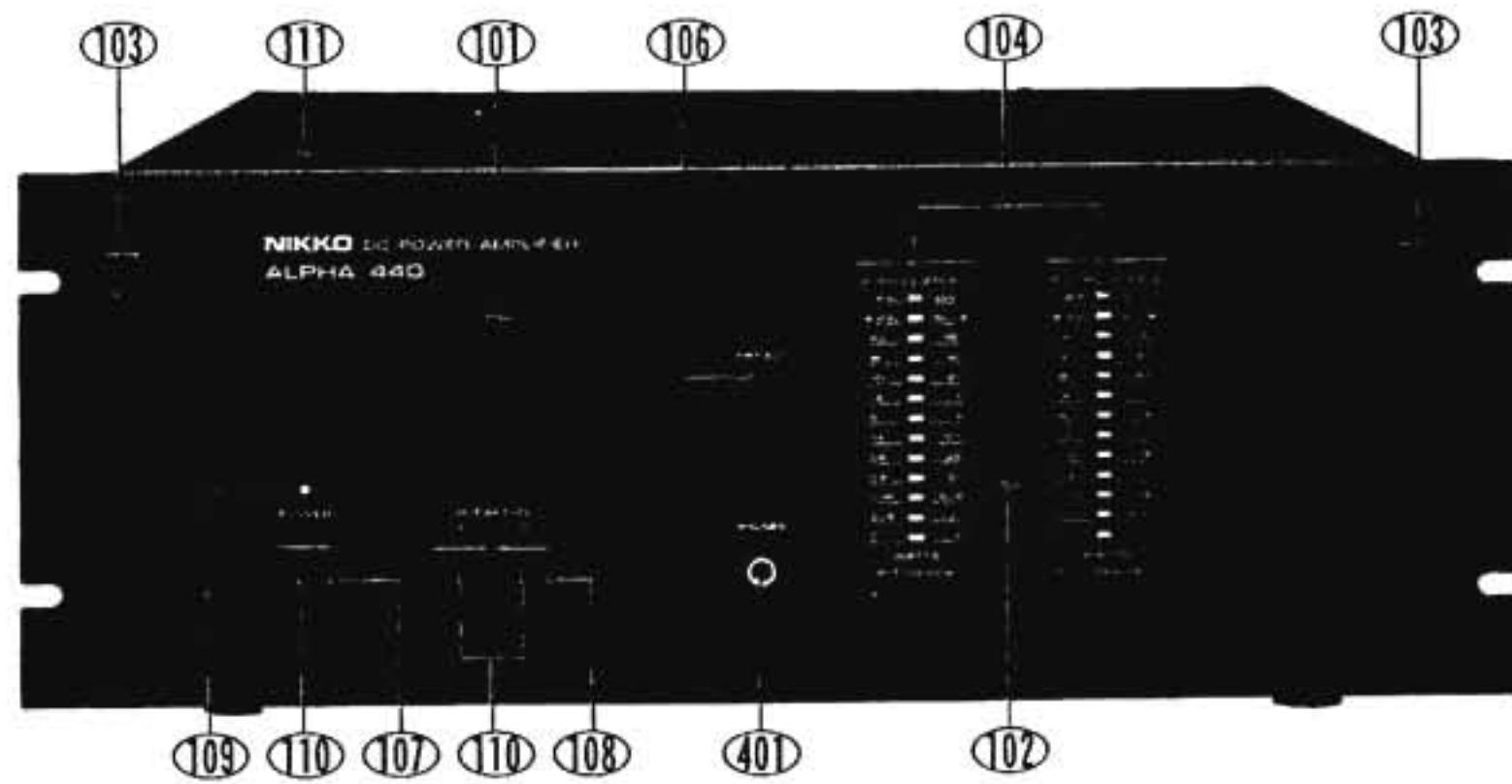


Photo 6

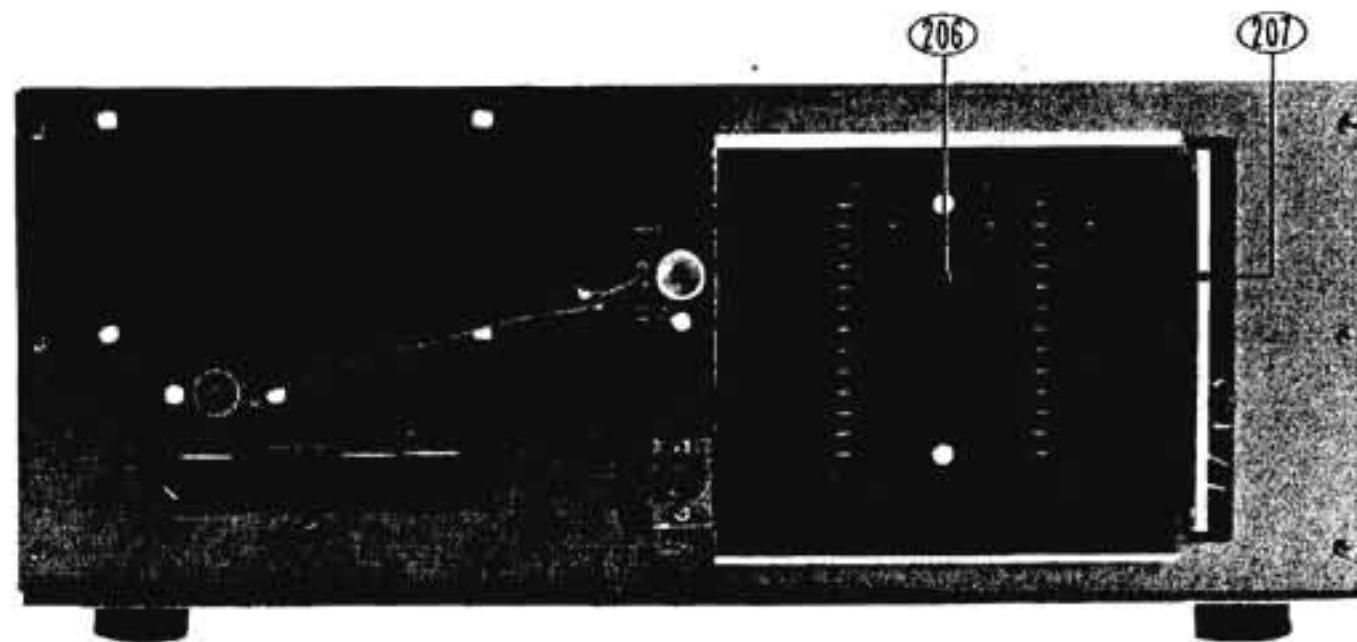


Photo 7



Photo 8

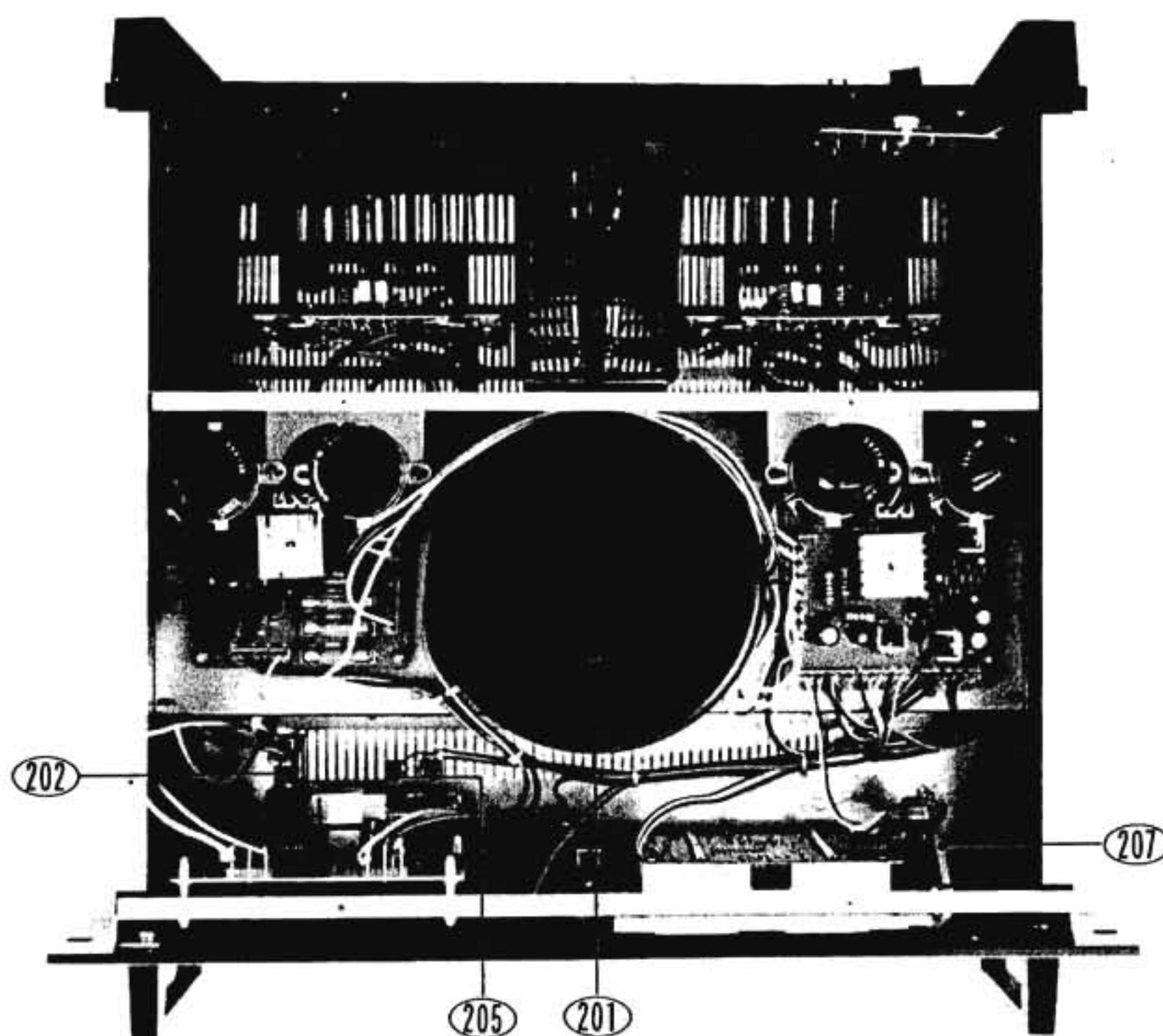


Photo 9

POWER TRANSISTORS MOUNTING ASSEMBLY

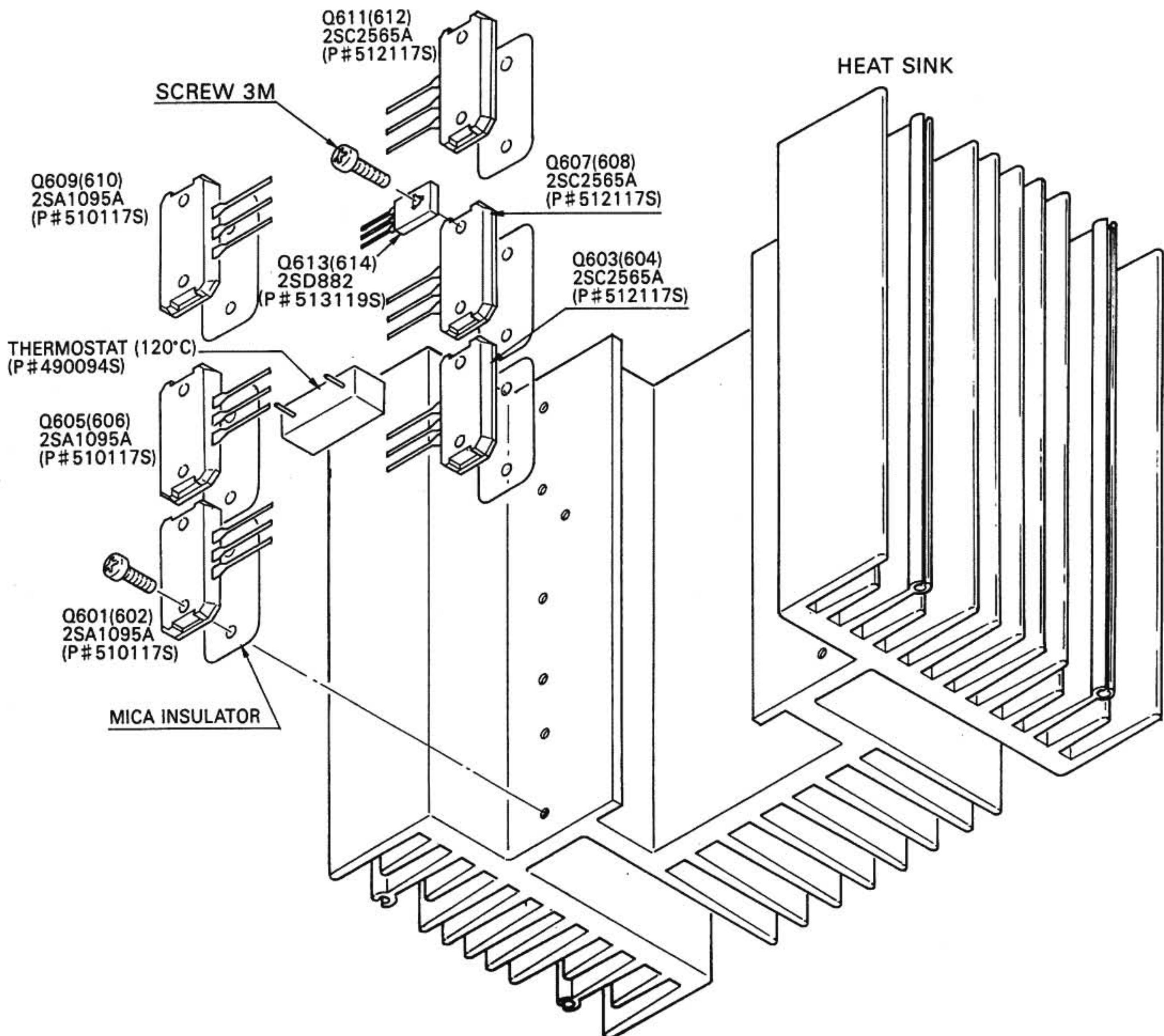


Figure 9

NOTE: For best heat conduction, use thermally conductive silicon grease between the power transistor and the mica insulator and between the insulator and the heat sink.

PRECAUTIONS FOR REPAIR SERVICE

Many of these items are included just as a reminder — they are normal procedures for experienced technicians. Short-cuts can be taken: but, often they cause additional damage to transistors, circuit components or the printed circuit board.

1. Do not bridge electrolytic capacitors with AC power. The resultant surges may damage solid state devices.
2. Do not bias the base of any transistor while voltage is being applied to its collector.

3. Replacements for output and driver transistors, if necessary, must be made from the same hfe group as the original type. Be sure to include this information when ordering replacement transistors.
4. If one output transistor burns out (open or shorts), always remove all output transistors in that channel and check the bias adjustment, the control and other parts in the network with an ohmmeter before inserting a new transistor. All output transistors in one channel will be destroyed if the base biasing circuit is open in the emitter end.

PARTS LIST

NOTES:

1. * The KEY NUMBER (#) marked with a (*) on parts list relate to number of three digits with a (). (Photo 6 ~ 9)
2. + Numerals in file indicate the quantity of parts used in one type.
3. ++ TR : Transistor
FET : Field effect transistor
VR : Volume control (Variable resistor)
RES : Carbon film fixed resistor
MO-RES : Metal oxide film fixed resistor
CEM-RES : Cemented wirewound fixed resistor
FP : Flame proof
C-CAP : Ceramic capacitor
E-CAP : Aluminum electrolytic capacitor
M-CAP : Polyester film capacitor
S-CAP : Polystyrene film capacitor
T-CAP : Tantalum electrolytic capacitor
BP-CAP : Bipolar electrolytic capacitor
LC-CAP : Low current leakage electrolytic capacitor.

4. Assemblies and parts are subject to change without notice.

5. Parts ordering procedure:

A. DO NOT USE THE "KEY" NUMBER AND "SYMBOL" NUMBER.
(these are control # for the factory only)

B. Include in any order

- a. Part number.
- b. Part description.
- c. Model number.

(any of the above lacking from an order may delay shipment of that order.)

CAUTION:

The mark, the KEY NO. and the SYMBOL NO. circled with rectangle in the schematic diagram and the shaded area in the parts list designate components which have special characteristics important for safety and should be replaced only with types identical to those in the original circuit or specified in the parts list.

KEY	SYMBOL	TYPE ⁺	DESCRIPTION ⁺⁺	PART
NO.	NO.	W E B		NO.
PACKING MATERIALS & ACCESSORIES				
001	1 1 1		Carton box	9825780
002	2 2 2		Pad	9840960
003	1 1 1		Sack, polyethylen cloth	9640750
004	1 1 1		Sack, polyethylen cloth - #13	9640320
005a	1 ---		Manual, instructions - English and French	960334E
005b	- 1 1		Manual, instructions - in five different languages	960335K
006	1 ---		Manual, safety instructions	9670410
007a	1 ---		Card, warranty - U.S.A.	967043A
007b	1 ---		Card, warranty - Canada	9670420
008	1 ---		List, service stations	9690180
009	1 1 1		Cord, RCA phono pin plug - 2T-1	962014A
CABINET ASSEMBLY				
*101a	1 1 1		Panel, front - SILVER	7884920
*101b	1 1 1		Panel, front - BLACK	7884930
*102a	1 1 1		Panel, power level indicator - SILVER	7870550
*102b	1 1 1		Panel, power level indicator - BLACK	7870410
*103a	2 2 2		Handle - 120G - SILVER	7490200
*103b	2 2 2		Handle - 120B - BLACK	7490210
*104	1 1 1		Window, panel	7802570
105	1 1 1		Spacer, LED	7002130
*106	1 1 1		Globe, LED - protection indicator	7402540
*107	1 1 1		Guide, button - 1P18 - power switch	7402550
*108	1 1 1		Guide, button - 2P18 - speakers selector	7402560
*109	1 1 1		Globe, LED - input power indicator	7402120
*110a	3 3 3		Button, Push - M18GL - power/speaker, SILVER	7852290
*110b	3 3 3		Button, push - M18BK - power/speaker, BLACK	7852300
*111	1 1 1		Cover, top	7821090
112	1 1 1		Plate, bottom	7326250
113	4 4 4		Foot, polyethylen - 30φx14	7400780
CHASSIS ASSEMBLY				
*201a	1 ---		Transformer, power - T-1-388 - AC120V	1103880
*201b	- 1 1		Transformer, power - T-1-389 - AC220 or 240V	1103890
*202a	1 ---		Switch, push - SDZ-1P TV-8 - power	4041500
*202b	- 1 1		Switch, push - ESB-70823S - power	4041600
*203a	1 ---		C-CAP 0.0047uf AC125V	239472C
*203b	- 1 1		C-CAP 0.0047uf AC250V	239472S
*204	- 1 1		Cover, C-CAP	7400960
*205	1 1 1		Switch, twin push - SUF-24 - speakers	4041040
*206	1 1 1		Inside panel, power level indicator	7802590
*207	1 1 1		Light guide, level indicator	7401580
*208	1 1 1		Lamp - 8V 0.3A	5808200

KEY	SYMBOL	TYPE ⁺	DESCRIPTION ⁺⁺	PART
NO.	NO.	W E B		NO.
BACK PLATE ASSEMBLY				
*301a	1 ---		Plate, back - (W)	7326280
*301b	- 1 1		Plate, back - (E)	7326290
*302	2 2 2		Block, terminal guard	7402130
*303	2 2 2		Knob - P2BK-162VD - input level	7851800
*304a	1 ---		Cord, AC line - SPT-2	606008A
*304b	- 1 -		Cord, AC line - CEE-2T	600511A
*304c	- 1 1		Cord, AC line - BS	600515A
*305a	1 ---		Bush, power cord - SR-4N-4	7400690
*305b	- 1 1		Bush, power cord - SR-6W-1	7400740
*306	1 1 1		Terminal, speakers - screw type 4P	4450480
*307	1 1 1		Shaft, GND terminal - MK-3	7152050
*308	1 1 1		Nut, GND terminal - MK-2	7152060
(INPUT PCB SECTION)				
*309	1 1 1		Terminal, RCA phono pin jack	4442070
*310	1 1 1		Switch, slide - SSB-042 - normal-direct selector	4020560
311	2 2 2		VR 100kohm (B) - input level control	4310630
C701,702	2 2 2		BP-CAP 0.47uf 50V	225505C
R701,702	2 2 2		RES 1meg·ohm 5% 1/4W	328105J
PRIMARY RELAY PC BOARD ASSEMBLY				
(PRIMARY RELAY SECTION)				
F901	1 ---		Fuse - 12A 250V MGC	4700750
F901	- 1 1		Midget fuse - T6.3A 250V	4720490
RY901	1 ---		Relay - LY1-0-US TV-5	1700340
RY901	- 1 1		Relay - FRL-264D100	
D901,902	2 ---		Diode S5277D	560047S
D901,902	- 2 2		Diode S5277G	560069S
C926	1 ---		C-E-CAP 47uf 63V	211625Q
C926	- 1 1		E-CAP 10uf 160V	261120Q
C934	1 1 1		CEM-RES 3.3ohm 10% 15W	387338U
R935	1 ---		FP-MO-RES 1.8kohm 5% 3W	363182L
R935	- 1 1		FP-MO-RES 6.8kohm 5% 3W	363682L
(INPUT POWER INDICATOR SECTION)				
LD928	1 1 1		LED BR5504S	5060300

PART ORDERING PROCEDURE ----- DO NOT USE THE "KEY" NUMBER AND "SYMBOL" NUMBER. (these are control # for the factory only.) Include in any order: a. Part number, b. Part description, c. Model number. (any of the above lacking from an order may delay shipment of the order.)

KEY	SYMBOL	TYPE ⁺			PART NO.
		NO.	NO.	WEB	
DESCRIPTION ⁺⁺					
		1 1 1	Spacer, LED		7903140
		(PROTECTION INDICATOR SECTION)			
LD927		1 1 1	LED PR5527S		5060270
		1 1 1	Spacer, LED		7903270
		(HEADPHONES SECTION)			
*401	R932,933	1 1 1	Jack, headphones		4550260
		2 2 2	FP-MO-RES 390ohm	5%	2W
					362391L
MAIN AMP PC BOARD ASSEMBLY					
L701,702		1 1 1	Coil, choke – 1uH		1210960
IC901,902		2 2 2	IC uPC741C		518088S
Q701					
~ Q704		4 4 4	TR 2SC1845 (E or F)		512115S
Q705,706		2 2 2	FET 2SK150A (GR)		516038S
Q707					
~ Q714		8 8 8	TR 2SC1845 (E or F)		512115S
Q715					
~ Q718		4 4 4	TR 2SB718 (C)		511117S
Q719,720		2 2 2	TR 2SC1845 (E or F)		512115S
Q721,722		2 2 2	TR 2SD758 (C)		513120S
Q723,724		2 2 2	TR 2SC1845 (E or F)		512115S
Q725					
~ Q728		4 4 4	TR 2SA992 (E or F)		510110S
Q729,730		2 2 2	TR 2SC1845 (E or F)		512115S
Q731,732		2 2 2	TR 2SA992 (E or F)		510110S
Q733					
~ Q740		6 6 6	TR 2SC1845 (E or F)		512115S
Q743,744		2 2 2	TR 2SD760 (B or C)		513121S
Q745,746		2 2 2	TR 2SB720 (B or C)		5111118S
D701					
~ D704		4 4 4	Diode 1S2076		501019S
ZD701					
~ ZD704		4 4 4	Zener diode RD30EB3		502066S
ZD901,902		2 2 2	Zener diode RD15EB2		502050S
TH701,702		2 2 2	Thermistor SDT-35		5400190
TH703,704		2 2 2	Thermistor D2FHL-103S		5400180
C703,704		2 2 2	E-CAP 10uf 100V		211820Q
C705,706		2 2 2	C-CAP 120pf 10% 50V SL		232121K
C707					
~ C710		4 4 4	E-CAP 10uf 35V		211420Q
C711,712		2 2 2	C-CAP 220pf 10% 50V SL		232221K
C713,714		2 2 2	C-CAP 5pf ± 0.5pf 500V SL		234509D
C715,716		2 2 2	C-CAP 1pf ± 0.5pf 500V SL		234109D
C717,718		2 2 2	C-CAP 220pf 10% 50V SL		232221K
C719,720		2 2 2	M-CAP 0.047uf 10% 100V		226473K
C721,722		2 2 2	E-CAP 10uf 100V		211820Q

KEY	SYMBOL	TYPE ⁺			PART NO.
		NO.	NO.	WEB	
DESCRIPTION ⁺⁺					
C723,724		2 2 2	C-CAP 1pf ± 0.5pf	500V	SL 234109D
C725,726		2 2 2	M-CAP 0.047uf	10%	200V 272473K
C727,728		2 2 2	M-CAP 0.0022uf	10%	50V 222222K
C729					
~ C732		4 4 4	C-CAP 22pf	10%	50V SL 232220K
C733					
~ C736		4 4 4	M-CAP 0.0056uf	10%	50V 222562K
C785,786		2 2 2	M-CAP 0.047uf	10%	100V 226473K
C901					
~ C904		4 4 4	BP-CAP 10uf	25V	215320C
C905,907		2 2 2	E-CAP 22uf	25V	211322Q
C909					
~ C912		4 4 4	C-CAP 0.01uf	+80, -20%	50V YG 231103Z
HVR701,702		2 2 2	Potentiometer – 200ohm		4301290
HVR703,704		2 2 2	Potentiometer – 1kohm		4301300
HVR901,902		2 2 2	Potentiometer – 10kohm		4301280
R703,704		2 2 2	RES 2.2kohm	5%	1/4W 328222J
R705,706		2 2 2	RES 100kohm	5%	1/4W 328104J
R707,708		2 2 2	RES 5.6kohm	5%	1/4W 328562J
R711					
~ R714		4 4 4	RES 27kohm	5%	1/4W 328273J
R715,716		2 2 2	RES 2.7kohm	5%	1/4W 328272J
R717,718		2 2 2	RES 2.2kohm	5%	1/4W 328222J
R719,720		2 2 2	FP-MO-RES 4.7kohm	5%	2W 362472L
R721,722		2 2 2	RES 5.6kohm	5%	1/4W 328562J
R723,724		2 2 2	RES 820ohm	5%	1/4W 328821J
R725,726		2 2 2	RES 560ohm	5%	1/4W 328561J
R727,728		2 2 2	RES 820ohm	5%	1/4W 328821J
R729,730		2 2 2	RES 2.2kohm	5%	1/4W 328222J
R731,732		2 2 2	RES 10kohm	5%	1/4W 328103J
R733,734		2 2 2	RES 4.7kohm	5%	1/4W 328472J
R735,736		2 2 2	FP-RES 120ohm	5%	1/4W 328121L
R737,738		2 2 2	FP-MO-RES 6.8kohm	5%	2W 362682L
R739,740		2 2 2	FP-MO-RES 4.7kohm	5%	2W 362472L
R741					
~ R744		4 4 4	FP-RES 220ohm	5%	1/4W 328221L
R745					
~ R748		4 4 4	RES 470ohm	5%	1/4W 328471J
R749					
~ R752		4 4 4	RES 1kohm	5%	1/4W 328102J
R755,756		2 2 2	FP-RES 47ohm	5%	1/4W 328470L
R757					
~ R760		4 4 4	RES 100ohm	5%	1/4W 328101J
R761,762		2 2 2	FP-MO-RES 47ohm	5%	1/4W 328470L
R763					
~ R766		4 4 4	RES 220ohm	5%	1/4W 328222L
R767					
~ R770		4 4 4	RES 1.5kohm	5%	1/4W 328152J
R771,772		2 2 2	FP-MO-RES 150ohm	5%	1W 361150L
R775,776		2 2 2	FP-MO-RES 10ohm	5%	2W 362100L
R793,794		2 2 2	CEM-RES 6.8ohm	10%	5W 384688K
R797,798		2 2 2	RES 22kohm	5%	1/4W 328223J
R901					
~ R904		4 4 4	RES 2.2kohm	5%	1/4W 328222J
R905,906		2 2 2	RES 120kohm	5%	1/4W 328124J
R907,908		2 2 2	RES 22kohm	5%	1/4W 328223J
R909,911		2 2 2	FP-MO-RES 4.7kohm	5%	2W 362472L
(PROTECTOR SECTION)					
RY801		1 1 1	Relay – DC48V		1700380
RY802,803		2 2 2	Relay – DC48V		1700330
		4 4 4	Magnet – 1285		7903170
Q801,802		2 2 2	TR 2SC1941 (L or K)		512112S
Q803		1 1 1	TR 2SA992 (E or F)		510110S
Q804,806		2 2 2	TR 2SC945L (P or Q)		515077S
Q805		1 1 1	TR 2SA733A (P or Q)		514074S
Q807		1 1 1	TR 2SC2240 (BL)		512116S
Q808		1 1 1	TR 2SB649 (B or C)		511111S
D801,802		2 2 2	Diode 1SS55		501024S
D803,804		2 2 2	Diode 1SS53		501023S
D805					
~					

PART ORDERING PROCEDURE ----- DO NOT USE THE "KEY" NUMBER AND "SYMBOL" NUMBER. (these are control # for the factory only.) Include in any order: a. Part number, b. Part description, c. Model number. (any of the above lacking from an order may delay shipment of the order.)

KEY NO.	SYMBOL NO.	TYPE ⁺ W E B	DESCRIPTION ⁺⁺	PART NO.
C801	1 1 1	E-CAP 1uf 50V		211510Q
C802	1 1 1	BP-CAP 33uf 6.3V		215053C
C803,804	2 2 2	E-CAP 100uf 16V		211230Q
C805	1 1 1	E-CAP 10uf 50V		211520Q
C806	1 1 1	E-CAP 4.7uf 35V		211415Q
REGULATOR (L) PC BOARD ASSEMBLY				
F831,832	2 --	Fuse - 2A 250V MGC		4700620
F833	1 --	Fuse - 1A 250V MGC		4700590
F831,832	-2 2	Midget fuse - T2A 250V		4720370
F833	-1 1	Midget fuse - T1A 250V		4720330
D831	1 1 1	Diode S10VB20		560058S
D832	1 1 1	Diode W02		560061S
C831,832	2 2 2	E-CAP 15000uf 100V		2100100
C833,834	2 2 2	E-CAP 1000uf 100V		2100110
R813,832	1 1 1	FP-MO-RES 4.7kohm 5% 2W		362472L
REGULATOR (R) PC BOARD ASSEMBLY				
Q809	1 1 1	TR 2SA985 (P or Q)		510118S
Q810,811	2 2 2	TR 2SA992 (E or F)		510110S
Q812	1 1 1	FET 2SK104 (F)		516026S
Q813	1 1 1	TR 2SC2275 (P or Q)		512120S
Q814,815	2 2 2	TR 2SC1845 (E or F)		512115S
Q816	1 1 1	FET 2SK104 (F)		516026S
Q817	1 1 1	TR 2SC2275 (P or Q)		512120S
Q818	1 1 1	TR 2SC1845 (E or F)		512115S
D802,803	2 2 2	Zener diode RD30EB3		502066S
D804	1 1 1	Zener diode RD15EB2		502050S
D833	1 1 1	Diode S5277B		560046S
D834	1 1 1	Diode S10VB20		560058S

KEY NO.	SYMBOL NO.	TYPE ⁺ W E B	DESCRIPTION ⁺⁺	PART NO.
C835,837	2 2 2	E-CAP 1uf 50V		211510Q
C836,837	2 2 2	E-CAP 3.3uf 35V		211413Q
C839	1 1 1	E-CAP 33uf 16V		211223Q
C840	1 1 1	E-CAP 47uf 63V		211625Q
C841,842	2 2 2	E-CAP 15000uf 100V		2100100
R833,837	1 1 1	RES 47kohm 5% 1W		328473J
R834,838	1 1 1	RES 33kohm 5% 1W		328333J
R835,839	1 1 1	RES 22kohm 5% 1W		328223J
R841	1 1 1	FP-MO-RES 3.3kohm 5% 2W		362332L
R842,843	2 2 2	FP-MO-RES 220ohm 5% 2W		362221L
R844	1 1 1	FP-MO-RES 4.7kohm 5% 1W		361472L
R845,846	2 2 2	FP-MO-RES 4.7kohm 5% 2W		362472L
POWER LEVEL INDICATOR PCB ASSEMBLY				
IC903,904	2 2 2	IC UAA180		518066S
IC905	1 1 1	IC TA7318P		518067S
ZD904	1 1 1	Zener diode RD6.2EB2		502048S
LD901				
~ LD922	2 2 2 2	LED PG5527SY - green		5060280
LD923				
~ LD926	4 4 4	LED PR5527S - red		5060270
C921,922	2 2 2	E-CAP 1uf 50V		211510Q
C923,924	2 2 2	M-CAP 0.0047uf 10% 50V		222472K
C925	1 1 1	E-CAP 1uf 50V		211510Q
HVR921,922	2 2 2	Potentiometer - 3kohm		4301340
R921,922	2 2 2	RES 47kohm 5% 1W		328473J
R923,924	2 2 2	RES 10kohm 5% 1W		328103J
R925				
~ R928	4 4 4	RES 1kohm 5% 1W		328102J
R929	1 1 1	RES 820ohm 5% 1W		328820J
R930	1 1 1	RES 3.3kohm 5% 1W		328322J
R931	1 1 1	RES 1.2kohm 5% 1W		328122J

SEMICONDUCTOR DATA

TRANSISTORS

t NOTES Ge: Germanium
Si: Silicon

A : Alloy	Df : Drift-field	M : Mesa
B : Base	E : Epitaxial	P : Planer
D : Diffused	G : Grown	Pc : Point-contact
Dd : Double-diffused	J : Junction	Td : Triple-diffused

DEVICE TYPE	APPLICATIONS	STRUCTURE†	MAXIMUM RATINGS Absolute-Maximum Values: (TA = 25°C unless otherwise specified)						ELECTRICAL CHARACTERISTICS Typical Values: (TA = 25°C unless otherwise specified)												MANUFACTURER
			Collector-to-Base Voltage VCBO (V)	Emitter-to-Base Voltage VEB (V)	Collector Current IC (mA)	Collector Dissipation PC (mW)	Junction Temperature TJ (°C)	Collector Cutoff Current ICBO (μA)	Static Forward-Current Transfer Ratio hFE	Collector-Emitter Saturation Voltage VCE(sat) (V)			Gain-Bandwidth Product fT (MHz)			Output Capacitance Cob (pF)	Others				
										VCE (V)	IC (mA)	IE (mA)	fT (MHz)	VCE (V)	IC (mA)	IE (mA)					
2SA733A (P, Q)	AF, General	PNP Si-E	-60	-5	-100	250	125	-0.1 max.	-60	135 ~ 400	-6	-1	-0.3 max.	-100	-10	450 max.	-6	10	6 max.	NEC	
2SA985 (P, Q)	AF, Power amp.	PNP Si-E	-120	-5	-1.5A (Tc=25°C)	25W	150	-1 max.	-120	100 ~ 320	-5	-300	-2 max.	-1A	-100	180	-5	-200*	29	Complementary to 2SC2275	NEC
2SA992 (E, F)	AF, Low noise	PNP Si-E	-120	-5	-50	500	125	-0.05 max.	-120	300 ~ 800	-6	-1	-0.3 max.	-10	-1	100	-6	1	3 max.	Complementary to 2SC1845	NEC
2SA1095A (R, O, Y)	AF, Power amp.	PNP Si-E	-180	-5	-15A (Tc=25°C)	150W	150	-50 max.	-160	55 ~ 240	-5	-1A	-2 max.	-5A	-500	60	-10	-1A*	350	Complementary to 2SC2565A	TOSHIBA
2SB649 (B, C)	AF, Driver	PNP Si-E	-180	-5	-1.5A (Tc=25°C)	20W	150	-10 max.	-160	60 ~ 200	-5	-150	-1 max.	-500	-50	140	-5	-150*	27	Complementary to 2SD758	HITACHI
2SB718 (C)	AF, Driver	PNP Si-E	-200	-5	-50	1250	150	-10 max.	-160	100 ~ 200	-5	-10	-2 max.	-30	-3	140	-5	-10*	5.5	Complementary to 2SD758	HITACHI
2SB720 (B, C)	AF, Driver	PNP Si-E	-200	-5	-2A (Tc=25°C)	25W	150	-10 max.	-160	60 ~ 200	-5	-150	-1 max.	-500	-50	100	-5	-150*	32	Complementary to 2SC760	HITACHI
2SC945L (P, Q)	AF, General	NPN Si-E	60	5	100	250	125	0.1 max.	60	135 ~ 400	6	1	0.3 max.	100	10	450 max.	6	-10	5 max.	NEC	
2SC1845 (E, F)	AF, Low noise	NPN Si-E	120	5	50	500	125	0.05 max.	120	300 ~ 800	6	1	0.3 max.	10	1	110	6	-1	2.5 max.	Complementary to 2SA992	NEC
2SC1941 (L, K)	AF, Driver	NPN Si-E	160	5	50	800	150	0.1 max.	160	135 ~ 400	10	1	0.6 max.	20	2	120	10	-10	3 max.	NEC	
2SC2275 (P, Q)	AF, Power amp.	NPN Si-E	120	5	1.5A (Tc=25°C)	25W	150	1 max.	120	100 ~ 320	5	300	2 max.	1A	100	200	5	200*	19	Complementary to 2SA985	NEC
2SC2565A (R, O, Y)	AF, Power amp.	NPN Si-E	180	5	15A (Tc=25°C)	150W	150	50 max.	160	55 ~ 240	5	1A	2 max.	5A	500	80	10	1A*	200	Complementary to 2SA1095A	TOSHIBA
2SD758 (C)	AF, Driver	NPN Si-E	200	5	50	1250	150	10 max.	160	100 ~ 200	5	10	2 max.	30	3	140	5	10*	3.8	Complementary to 2SB718	HITACHI
2SD760 (B, C)	AF, Driver	NPN Si-E	200	5	2A (Tc=25°C)	25W	150	10 max.	160	60 ~ 200	5	150	1 max.	500	50	100	5	150*	21	Complementary to 2SB720	HITACHI
2SD882 (P, Q)	AF	NPN Si-E	40	5	3A (Tc=25°C)	10W	150	1 max.	30	100 ~ 320	2	20	0.5 max.	2A	200	90	5	-100	45		NEC

FIELD EFFECT TRANSISTORS

DEVICE TYPE	APPLICATIONS	STRUCTURE†	MAXIMUM RATINGS Absolute-Maximum Values: (TA = 25°C unless otherwise specified)						ELECTRICAL CHARACTERISTICS Typical Values: (TA = 25°C unless otherwise specified)												MANUFACTURER	
			Gate-to-Drain Voltage VGDO (V)	Gate-to-Source Voltage VGS0 (V)	Gate Current IG (mA)	Drain Current ID (mA)	Total Dissipation PD (mW)	Channel Temperature Tch (°C)	Gate Leak Current Test Conditions	Gate to Drain Breakdown Voltage VBRH GDO (V)	Drain Current Test Conditions	Gate to Source Cutoff Voltage VGS (loff) (V)	Forward Transfer Admittance Test Conditions	Feed Back Capacitance Test Conditions	Power Gain (Common Source) Gps (dB)	Noise Figure Test Conditions NF (dB)						
2SK104 (H)	AF, General	Si N-channel junction	-50	-50	10	20	250	125	V _{GS} = -30V V _{DS} =0	-1 max.		V _{DS} =5V V _{GS} =0	2~6	V _{DS} =5V I _D =10μA	-1.1	V _{DS} =5V I _D =0.5mA f=1 kHz	2.1	V _{DS} =10V V _{GS} =0 f=1 MHz	0.9			NEC
2SK150-A (GRI)	AF, Low noise Differential amp.	Si N-channel junction (Dual)	-50	-50	10		200/unit	125	V _{GS} = -30V V _{DS} =0	-1 max.		V _{DS} =10V V _{GS} =0	2.6 ~ 6.5			V _{DS} =10V V _{GS} =0 f=1kHz I _{DSS} = 3mA	12	V _{DS} =10V I _D =0 f=1MHz	3	V _{DS} =10V R _g =1kΩ I _D =1mA f=1kHz	2 max.	TOSHIBA

DIODES, LED'S

DEVICE TYPE	APPLICATIONS	STRUCTURE†	MAXIMUM RATINGS Absolute - Maximum Values: (TA = 25°C unless otherwise specified)								ELECTRICAL CHARACTERISTICS Typical Values: (TA = 25°C unless otherwise specified)								MANUFACTURER		
			Reverse Surge Voltage VRsurge (V)	Peak Reverse Voltage VR (V)	Peak Forward Voltage VF (V)	Peak Forward Current IFM (mA)	Average Rectified Current IO (mA)	Forward Surge Current IF surge (A)	Junction Temperature TJ (°C)	Total Power Dissipation PD (mW)	Forward Current IFmin (mA)	Forward Voltage VFmax (V)	Reverse Current IRmax (μA)	Test Condition	Forward Current IF (mA)	Forward Voltage VF (V)	Reverse Current IR (μA)	Test Condition	Others		
1SS53	Medium speed switching	Si-EP		35	30		300	100	2	200	500			0.8	1.0	30	0.1	30		NEC	
1SS55	Medium speed switching	Si-EP			100	75		300	100	2	200	500			0.8	1.0	30	0.1	75		NEC
S52778	Rectifier	Si-DJ		100				2.0A	1.0A	50A	150		</td								

INTEGRATED CIRCUITS μ PC741C

- Manufacturer: NEC
- Applications: Operational Amplifier

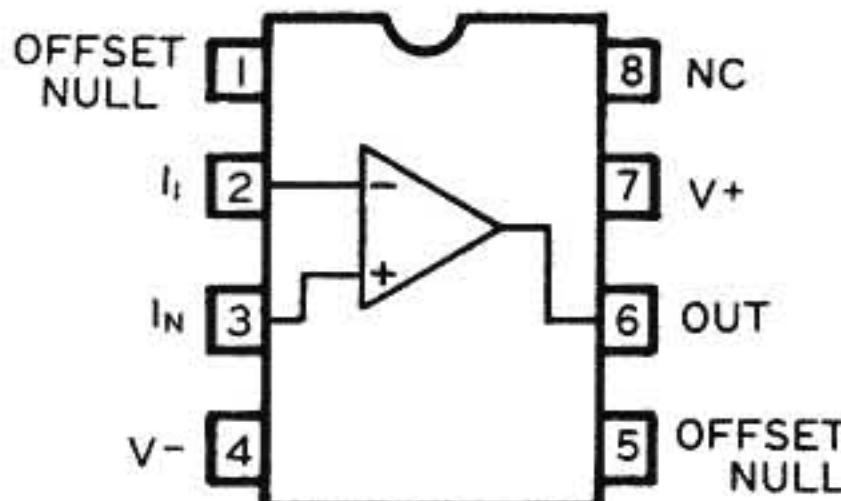
ABSOLUTE MAXIMUM RATINGS

Supply Voltage	± 18 V	Input Voltage	± 15 V
Internal Power Dissipation	350 mW	Storage Temperature Range	-40°C to +125°C
Differential Input Voltage	± 30 V	Operating Temperature Range	-20°C to +75°C

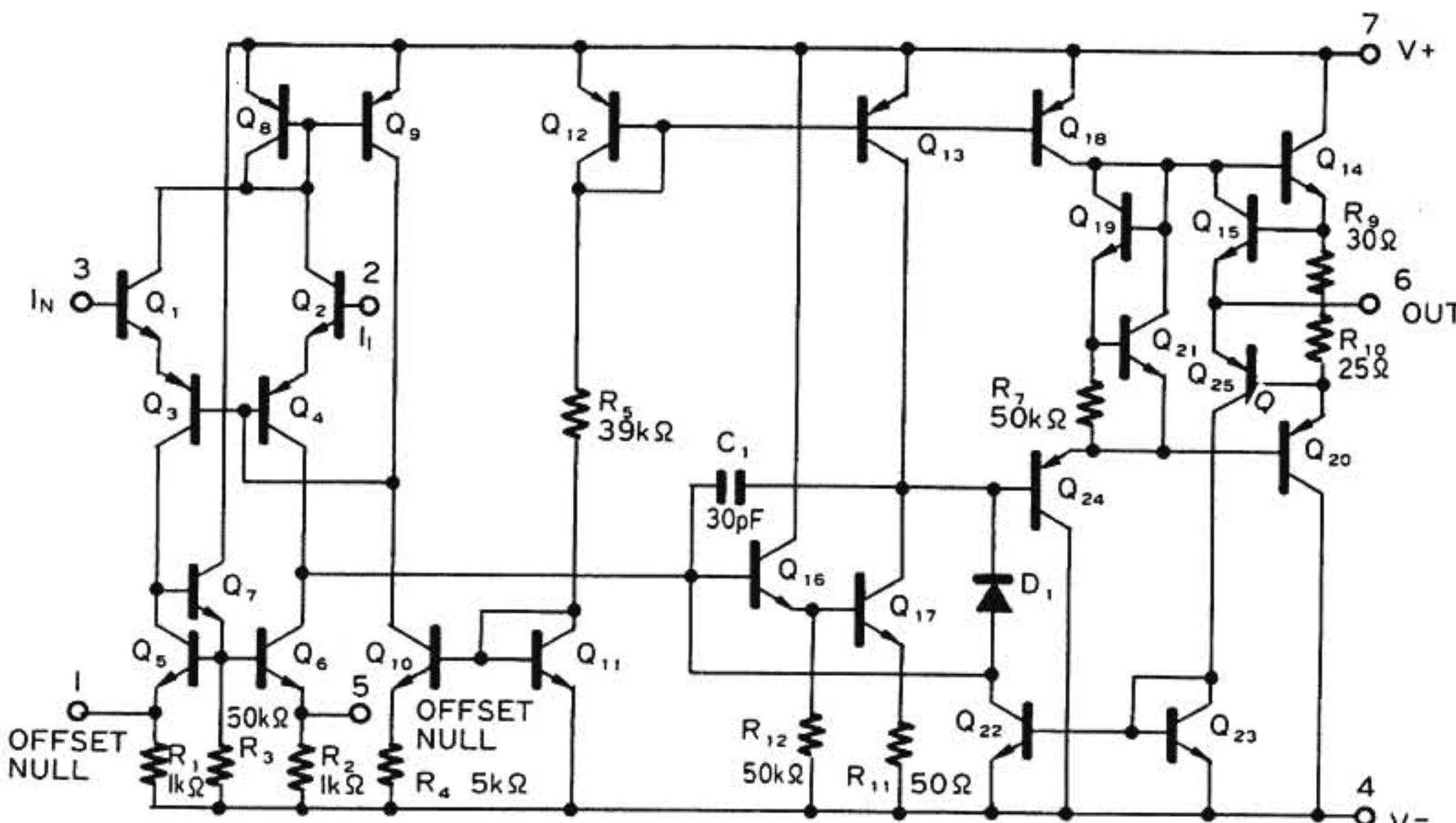
ELECTRICAL CHARACTERISTICS ($V_{CC} = \pm 15$ V, $T_A = +25^\circ\text{C}$ unless otherwise noted.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$		1.0	6.0	mV
Input Offset Current			20	200	nA
Input Bias Current			80	500	nA
Large-Signal Voltage Gain	$R_L \geq 2 \text{ k}\Omega$ $V_{out} = \pm 10$ V	108	106		dB
Output Voltage Swing	$R_L \geq 10 \text{ k}\Omega$	12	± 14		V
Common Mode Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$	70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$		30	150	$\mu\text{V/V}$
Power Consumption			45	85	mW

TERMINAL GUIDE (TOP VIEW)



EQUIVALENT CIRCUIT

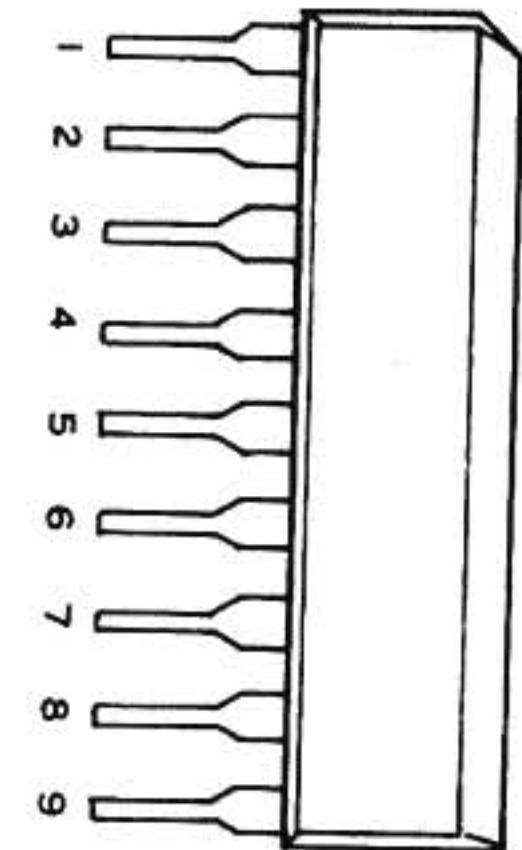
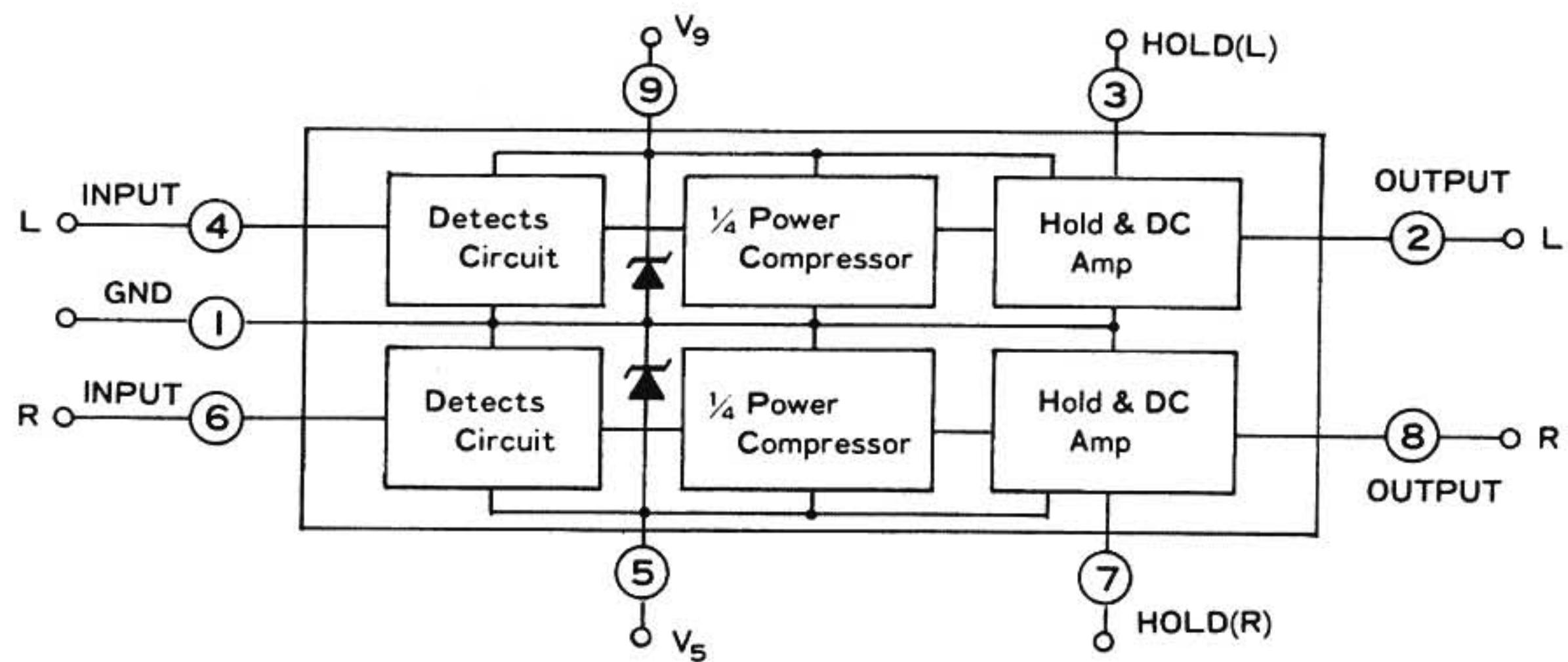


INTEGRATED CIRCUITS TA7318P

FUNCTION/MANUFACTURER

- Dual Linear-to-Log Converter for Peak Power Indicator/Toshiba

BLOCK DIAGRAM AND CONNECTION INFORMATION

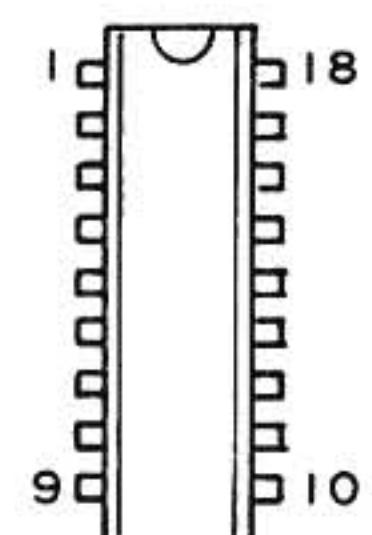
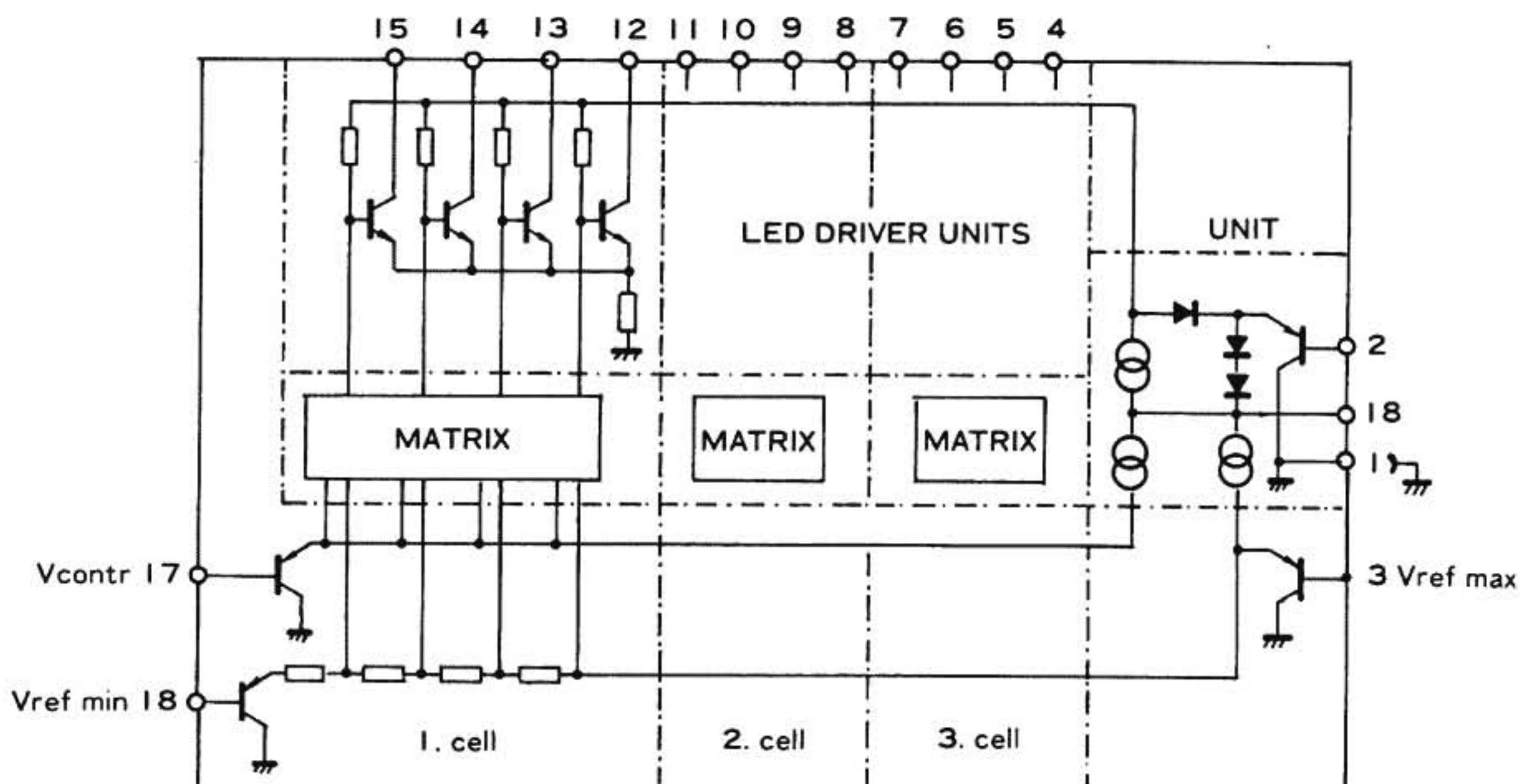


INTEGRATED CIRCUITS UAA180

FUNCTION/MANUFACTURER

- Analog-to-Digital Converter; 12 LED Driver/Siemens

BLOCK DIAGRAM AND CONNECTION INFORMATION



Important Information for your Parts and Service Department

MODEL: ALPHA 440

ASSEMBLY: DRIVER PCB

Several Alpha 440 Driver PCB's (#4631550) MAY employ a 3pf C-Cap at C716 and C723. This value (3pf) should be changed to a lpf in order to prevent oscillation.

The protection circuit on the same pcb (#4631550) employs a 10K ohm $\frac{1}{4}$ watt resistor at R817 and R819. The current flow at this value (10K ohm) causes the resistor to open, therefore the value should be changed to 33K ohm $\frac{1}{4}$ watt.

PARTS LIST

DELETE		
SYMBOL No.	DESCRIPTION	PART No.
C716	Ceramic capacitor	
C723	3pf 500v	-----
R817	Carbon film resistor	
R819	10K ohm $\frac{1}{4}$ watt	328103J

ADD		
SYMBOL No.	DESCRIPTION	PART No.
C716	Ceramic capacitor	
C723	1pf 500v	234109D
R817	Carbon film resistor	
R819	33K ohm $\frac{1}{4}$ watt	328330J

NIKKO ELECTRIC MFG. CO., LTD.

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 SALES OFFICE Mitsubishi Bank Bldg., 3-2, Dogenzaka 1-chome, Shibuya-ku, Tokyo 150, Japan

NIKKO ELECTRIC CORP. OF AMERICA

HEAD OFFICE 320 Oser Ave., Hauppauge, N.Y. 11787, U.S.A.
 L.A. OFFICE 7801 East Compton Blvd., Paramount, Ca. 90723, U.S.A.

Important Information for your Parts and Service Department

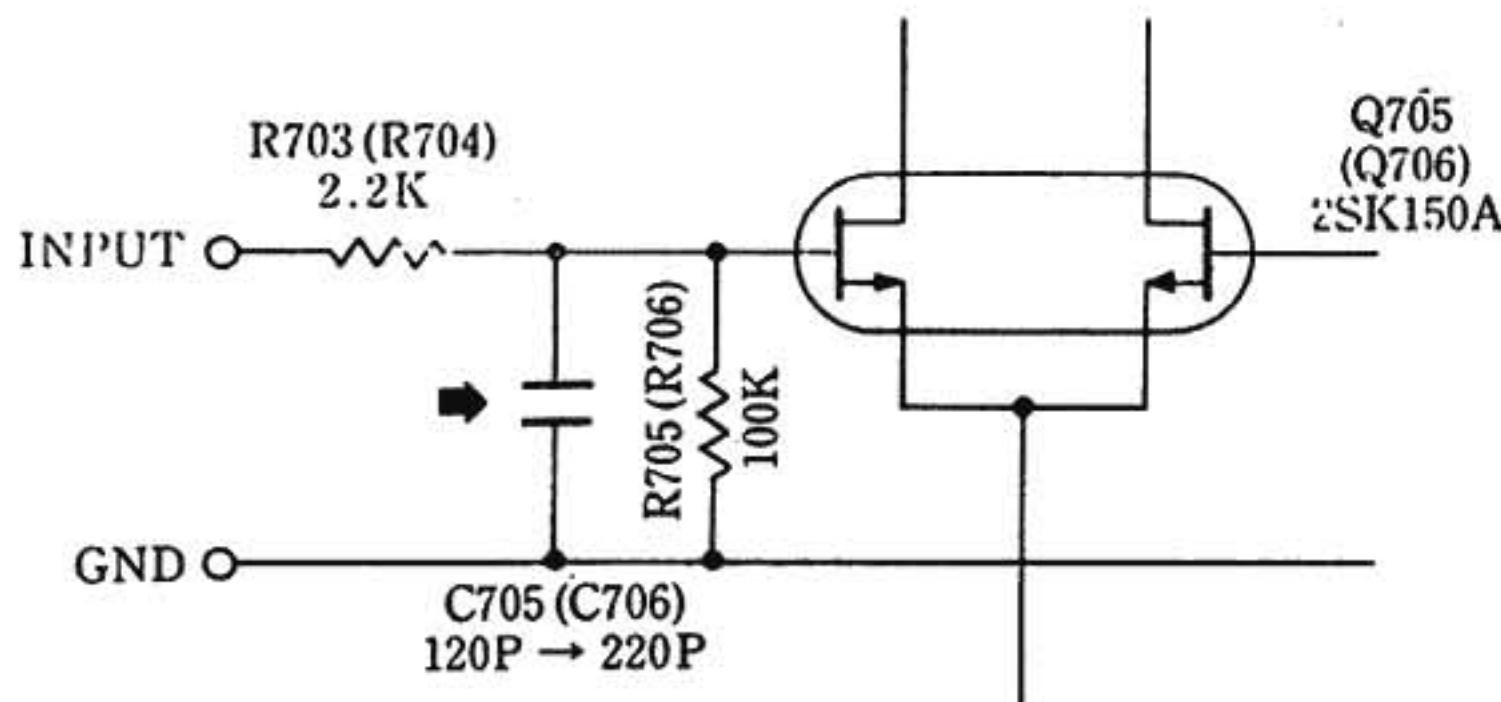
MODEL: ALPHA 440

ASSEMBLY: MAIN AMP PCB

For the purpose of protecting the transistors in the power stage, replace capacitors on the MAIN AMP P.C. BOARD.

* Capacitors C705 and C706 (120 pf) are replaced with new ones (220 pf).

These modifications are already done for the units bearing Serial No. C7532001 and up.

**PARTS LIST**

DELETE		
SYMBOL No.	DESCRIPTION	PART No.
C705,706	Ceramic capacitor 120pf 10% 50V	232121K

ADD		
SYMBOL No.	DESCRIPTION	PART No.
C705, 706	Ceramic capacitor 220pf 10% 50V	232221K

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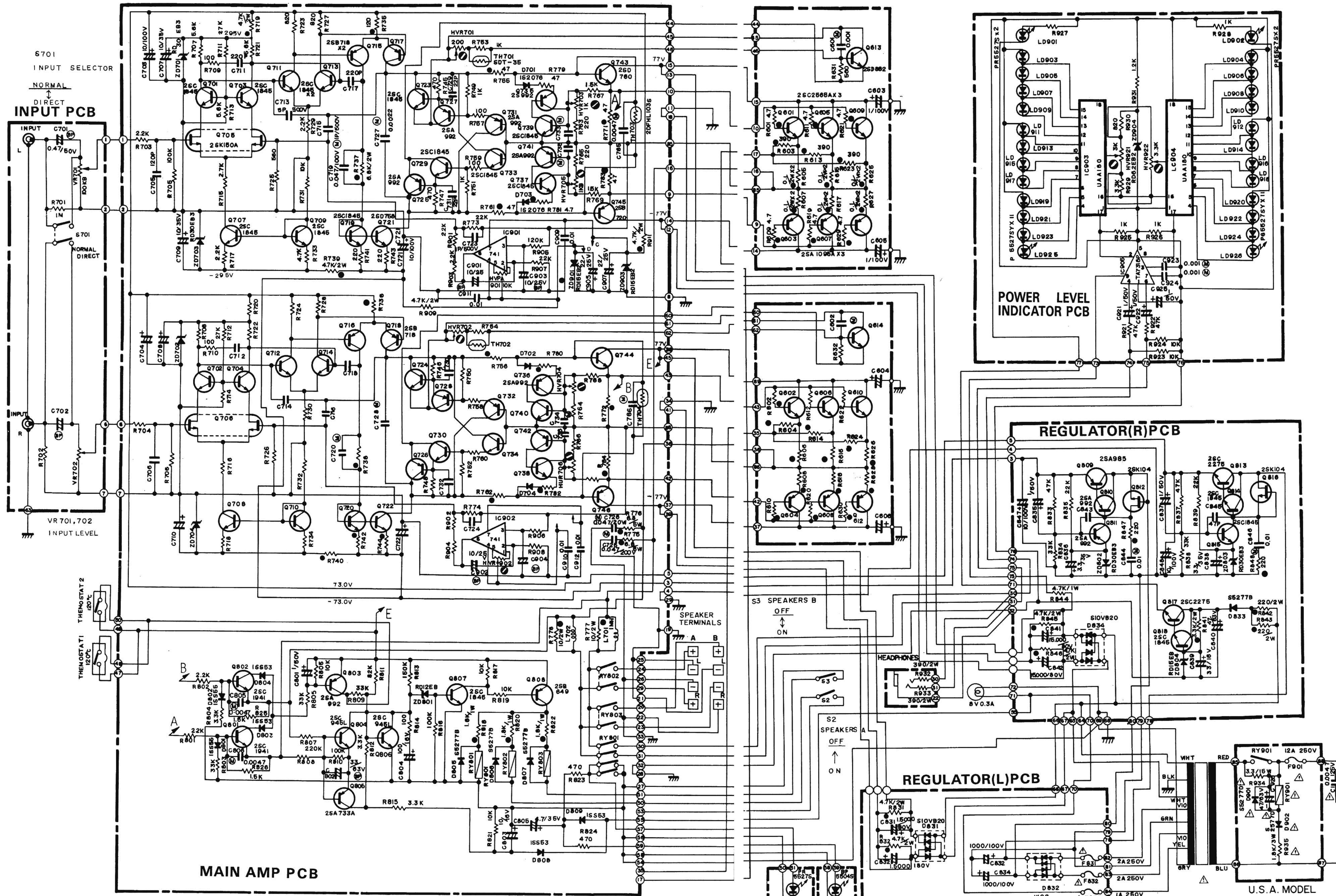
HEAD OFFICE

320 Oser Ave., Hauppauge, N.Y. 11787, U.S.A.

L.A. OFFICE

16270 Raymer St., Van Nuys, Ca. 91406, U.S.A.

SCHEMATIC DIAGRAM



NOTES:

- 1. SCHEMATIC IS SUBJECT TO CHANGE
WITHOUT NOTICE.**

UNLESS OTHERWISE SPECIFIED:

2. RESISTANCE VALUES ARE IN OHMS.
 $K = 1,000$; $M = 1,000,000$

**3. CAPACITANCE VALUES 1.0 AND ABOVE
ARE IN pF OR μ F (P = pF, M = μ F). LESS**

THAN 1.0 ARE IN μ F. (ELECTROLYTIC CAPACITANCE VALUES ARE IN μ F/WV.)

4. VOLTAGES ARE MEASURED TO CHASSIS GROUND WITH A "DC VOLTMETER"

SCHEMATIC SYMBOLS:

- M POLYESTER FILM CAPACITOR
 - BP BIPOLAR CAPACITOR
 - NONFLAMMABLE RESISTOR

McDANIEL

WARNING:
▲ INDICATES SAFETY CRITICAL COMPONENTS.
FOR CONTINUED SAFETY, REPLACE SAFETY CRITICAL COMPONENT
ONLY WITH MANUFACTURER'S RECOMMENDED PARTS.

Figure 7